

# SGM41518 High Input Voltage, 1.26A Single-Cell Battery Charger with NVDC Power Path Management

#### **FEATURES**

- High Efficiency, 1.5MHz, Synchronous Buck Charger
  - 95% Charge Efficiency at 1A from 5V Input
  - Selectable PFM Mode for Light Load Efficiency
- Boost Mode Support
  - Boost Efficiency of 95.5% at 0.5A and 95% at 1A
  - PMID\_GD Pin Control External P-MOSFET for Protection against Fault Conditions
  - Selectable PFM Mode for Light Load Operations
- Single Input for USB or High Voltage Adapters
  - 3.9V to 13.5V Operating Input Voltage Range
  - 22V Absolute Maximum Input Voltage Rating
  - Programmable Input Current Limit and Dynamic Power Management (IINDPM, 100mA to 3.2A with 100mA Resolution) to Support USB 2.0 and USB 3.0 Standards and High Voltage Adaptors
  - Maximum Power Tracking by Programmable Input
     Voltage Limit (VINDPM) with Selectable Offset
  - VINDPM Tracking of Battery Voltage
- High Battery Discharge Efficiency with 10mΩ Switch
- Narrow Voltage DC (NVDC) Power Path Management
  - Instant-On with No or Highly Depleted Battery
  - Ideal Diode Operation in Battery Supplement Mode
- Ship Mode, Wake-Up and Full System Reset Capability by Battery FET Control
- Flexible Autonomous and I<sup>2</sup>C Operation Modes for Optimal System Performance
- Fully Integrated Switches, Current Sense and Compensation

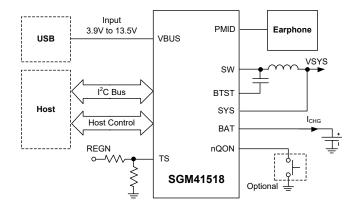
- External Direct Charging Path Enable Output
- 9µA Ship Mode Low Battery Leakage Current
- High Accuracy
- ±0.5% Charge Voltage Regulation (8mV/step)
- ±5% Charge Current Regulation at 1.26A
- + ±7.5% Input Current Regulation at 0.5A
- Safety
  - Battery Temperature Sensing (Charge/Boost Modes)
  - Thermal Regulation and Thermal Shutdown
  - Input Under-Voltage Lockout (UVLO)
  - Input Over-Voltage (ACOV) Protection

#### **APPLICATIONS**

Smart Phones, EPOS

Portable Internet Devices and Accessory

#### SIMPLIFIED SCHEMATIC





#### **GENERAL DESCRIPTION**

The SGM41518 is a battery charger and system power path management device with integrated converter and power switches for using with single-cell Li-lon or Li-polymer batteries. This highly integrated 1.26A device is capable of fast charging and supports a wide input voltage range suitable for wearable and earphone applications. I<sup>2</sup>C programming makes it a very flexible powering and charger design solution.

The device includes four main power switches: input reverse blocking FET (RBFET, Q1), high-side switching FET for Buck or Boost mode (HSFET, Q2), low-side switching FET for Buck or Boost mode (LSFET, Q3) and battery FET that controls the interconnection of the system and battery (BATFET, Q4). The bootstrap diode for the high-side gate driving is also integrated. The internal power path has a very low impedance that reduces the charging time and maximizes the battery discharge efficiency. Moreover, the input voltage and current regulations provide maximum charging power delivery to the battery with various types of input sources.

A wide range of input sources are supported, including standard USB hosts, charging ports and USB compliant high voltage adapters. The SGM41518 is USB 2.0 and USB 3.0 power specifications compliant with input current and voltage regulation. This limit is determined by the detection circuit in the system (e.g. USB PHY).

The SGM41518 is capable to boost the battery voltage to supply 5V (adjustable 4.85V/5V/5.15V/5.3V) on PMID. The Boost mode is used to charge another battery by the control of PMID\_GD. The PMID\_GD pin is used to drive an external P-MOSFET to disconnect Boost output PMID from attached accessories.

The system voltage is regulated slightly above the battery voltage by the power path management circuit and is kept above the programmable minimum system voltage (3.5V by default). Therefore, system power is maintained even if the battery is completely depleted or removed. Dynamic power

management (DPM) feature is also included that automatically reduces the charge current if the input current or voltage limit is reached. If the system load continues to increase after reduction of charge current down to zero, the power path management provides the deficit from battery by discharging battery to the system until the system power demand is fulfilled. This is called supplement mode, which prevents the input source from overloading.

Starting and termination of a charging cycle can be accomplished without software control. The sensed battery voltage is used to decide for starting phase of charging in one of the three phases of charging cycle: pre-conditioning, constant current or constant voltage. When the charge current falls below a preset limit and the battery voltage is above recharge threshold, the charger function will automatically terminate and end the charging cycle. If the voltage of a charged battery falls below the recharge threshold, the charger begins another charging cycle.

Several safety features are provided in the SGM41518 such as over-voltage and over-current protections, battery temperature monitoring, charging safety timing, thermal shutdown and input UVLO. TS pin is connected to an NTC thermistor for battery temperature monitoring and protection in both charge and Boost modes according to JEITA profile. This device also features thermal regulation in which the charge current is reduced, if the junction temperature exceeds 80°C or 120°C (selectable).

Charging status is reported by the STAT output and fault/status bits. A negative pulse is sent to the nINT output pin as soon as a fault occurs to notify the host. BATFET reset control is provided by nQON pin to exit ship mode or for a full system reset.

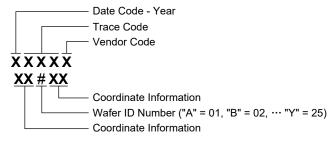
The SGM41518 is available in a Green WLCSP-2.0×2.4-30B package.

#### PACKAGE/ORDERING INFORMATION

MODEL	PACKAGE DESCRIPTION	SPECIFIED TEMPERATURE RANGE	ORDERING NUMBER	PACKAGE MARKING	PACKING OPTION
SGM41518	WLCSP-2.0×2.4-30B	-40°C to +85°C	SGM41518YG/TR	SGM 41518 XXXXX XX#XX	Tape and Reel, 3000

#### MARKING INFORMATION

NOTE: XXXXX = Date Code, Trace Code and Vendor Code.



Green (RoHS & HSF): SG Micro Corp defines "Green" to mean Pb-Free (RoHS compatible) and free of halogen substances. If you have additional comments or questions, please contact your SGMICRO representative directly.

#### **ABSOLUTE MAXIMUM RATINGS**

Voltage Range (with Respect to GND)
VAC, VBUS (Converter Not Switching)2V to 22V (1)
BTST, PMID (Converter Not Switching)0.3V to 22V
SW2V to 16V
SW (Peak for 10ns Duration)3V to 16V
BTST to SW0.3V to 6V
REGN, TS, nCE, BAT, BATSNS, SYS (Converter Not
Switching)0.3V to 6V
SDA, SCL, nINT, nQON, STAT, PMID_GD0.3V to 6V
Output Sink Current
STAT6mA (MAX)
nINT6mA (MAX)
Package Thermal Resistance
WLCSP-2.0×2.4-30B, $\theta_{JA}$ 68°C/W
Junction Temperature+150℃
Storage Temperature Range65°C to +150°C
Lead Temperature (Soldering, 10s)+260℃
ESD Susceptibility
HBM2000V
CDM1000V

NOTE: 1. Maximum 28V for 10 seconds.

#### **DISCLAIMER**

SG Micro Corp reserves the right to make any change in circuit design, or specifications without prior notice.

#### RECOMMENDED OPERATING CONDITIONS

Input Voltage Range, V <sub>VBUS</sub>	3.9V to 13.5V
Input Current (VBUS), I <sub>IN</sub>	3.4A (MAX)
Output DC Current (SW), I <sub>SWOP</sub>	3.25A (MAX)
Battery Voltage, V <sub>BATOP</sub>	4.624V (MAX)
Fast Charging Current, I <sub>CHGOP</sub>	1.26A (MAX)
Discharging Current (Continuous), IBATOP	6A (MAX)
Ambient Temperature Range	40°C to +85°C
Junction Temperature Range	40°C to +125°C

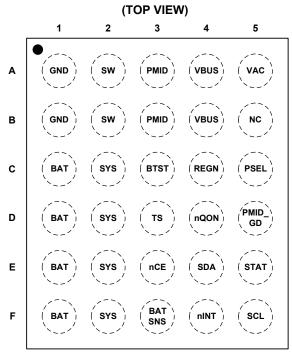
#### **OVERSTRESS CAUTION**

Stresses beyond those listed in Absolute Maximum Ratings may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect reliability. Functional operation of the device at any conditions beyond those indicated in the Recommended Operating Conditions section is not implied.

#### **ESD SENSITIVITY CAUTION**

This integrated circuit can be damaged if ESD protections are not considered carefully. SGMICRO recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because even small parametric changes could cause the device not to meet the published specifications.

#### **PIN CONFIGURATION**



WLCSP-2.0×2.4-30B

#### **PIN DESCRIPTION**

PIN	NAME	TYPE (1)	FUNCTION
A1, B1	GND	_	Ground Pin of the Device.
C1, D1 E1, F1	BAT	Р	Battery Positive Terminal Pin. Use a 10µF capacitor between BAT and GND pins close to the device. SYS and BAT pins are internally connected by BATFET with current sensing capability.
A2, B2	SW	Р	Switching Node Output. Connect SW pin to the output inductor. Connect a 47nF bootstrap capacitor from SW pin to BTST pin.
C2, D2 E2, F2	SYS	Р	Connection Point to Converter Output. SYS is connected to the converter LC filter output that powers the system. BAT to SYS internal current (power from battery to system) is sensed. Connect a $20\mu F$ capacitor between SYS pin and GND close to the device (in addition to $C_{OUT}$ ).
A3, B3	PMID	Р	PMID Pin. PMID is the actual higher voltage port of converter (Buck or Boost) and is connected to the drain of the reverse blocking MOSFET (RBFET) and the drain of HSFET. Connect a 22µF ceramic capacitor from PMID pin to GND. It is the proper point for decoupling of high frequency switching currents.
C3	BTST	Р	High-side Driver Positive Supply. It is internally connected to the boost-strap diode cathode. Use a 47nF ceramic capacitor from SW pin to BTST pin.
D3 TS AI		AI	Temperature Sense Input Pin. Connect to the battery NTC thermistor that is grounded on the other side. To program operating temperature window, it can be biased by a resistor divider between REGN and GND. Charge suspends if TS voltage goes out of the programmed range. It is recommended to use a 103AT-2 type thermistor. If NTC or TS pin function is not needed, use a $10k\Omega/10k\Omega$ pair for the resistor divider.
E3	nCE	DI	Charge Enable Input Pin (Active Low). Battery charging is enabled when CHG_CONFIG bit is 1 and nCE pin is pulled low.
F3	BATSNS	AIO	Battery Voltage Sensing Pin for Charge Current Regulation. BATSNS pin is connected to the actual battery pack as close as possible to reduce the parasitic trace resistance during charging.

### **PIN DESCRIPTION (continued)**

PIN	NAME	TYPE (1)	FUNCTION
A4, B4	VBUS	Р	Charger Input (V <sub>IN</sub> ). The internal N-channel reverse blocking MOSFET (RBFET) is connected between VBUS and PMID pins. Place a 1µF ceramic capacitor from VBUS pin to GND close to the device.
C4	REGN	Р	LDO Output that Powers LSFET Driver and Internal Circuits. Internally, the REGN pin is connected to the anode of the bootstrap diode. Place a 4.7µF (10V rating) ceramic capacitor between REGN pin and GND. It is recommended to place the capacitor close to the REGN pin.
D4	nQON	DI	BATFET On/Off Control Pin. Use an internal pull-up to a small voltage for maintaining the default high logic (whenever a source or battery is available). In the ship mode, the BATFET is off. To exit ship mode and turn BATFET on, a logic low pulse with a duration of t <sub>SHIPMODE</sub> (1s TYP) can be applied to nQON. When VBUS source is not connected, a logic low pulse with a duration of t <sub>QON_RST</sub> (10s TYP) resets the system power (SYS) by turning BATFET off for t <sub>BATFET_RST</sub> (320ms TYP) and then back on to provide a full power reset for system.
E4	SDA	DIO	$I^2$ C Data Signal. Use a 10k $\Omega$ pull-up to the logic high rail.
F4	nINT	DO	Open-Drain Interrupt Output Pin. Use a $10k\Omega$ pull-up to the logic high rail. The nINT pin is active low and sends a negative $256\mu s$ pulse to inform host about a new charger status update or a fault.
A5	VAC	Al	Sense Input for DC Input Voltage (Typically from an AC/DC Adaptor). Must be connected to VBUS pin.
B5	NC	_	No Connection.
C5	PSEL	DI	Power Source Selection Input. If PSEL is pulled high, the input current limit is set to 500mA (USB 2.0) and if it is pulled low, the limit is set to 2.4A (adaptor). When the I <sup>2</sup> C link to the host is established, the host can program a different input current limit value by writing to the IINDPM[4:0] register.
D5	D5 PMID_GD DO		Open-Drain PMID Good Indicator. Active high. Connect a $10k\Omega$ resistor to the pull-up rail REGN. HIGH indicates PMID voltage is below 6V and the current through Q1 is below 106% of input current limit. If the Boost mode output voltage is too high or output current is too high, the signal can be used to drive external P-MOSFET to disconnect the PMID under charging load.
E5	STAT	DO	Open-Drain Charge Status Output. Use a $10k\Omega$ pull-up to the logic high rail (or an LED + a resistor). The STAT pin acts as follows: During charge: low (LED ON). Charge completed or charger in sleep mode: high (LED OFF). Charge suspended (in response to a fault): 1Hz, 50% duty cycle pulses (LED BLINKS). The function can be disabled via EN_ICHG_MON[1:0] register.
F5	SCL	DI	$I^2$ C Clock Signal. Use a 10k $\Omega$ pull-up to the logic high rail.

#### NOTE:

1. Al = Analog Input, AO = Analog Output, AIO = Analog Input and Output, DI = Digital Input, DO = Digital Output, DIO = Digital Input and Output, DIO = Digita

#### **ELECTRICAL CHARACTERISTICS**

 $(V_{VAC\_UVLOZ} < V_{VAC} < V_{VAC\_OV} \text{ and } V_{VAC} > V_{BAT} + V_{SLEEP}, T_J = -40^{\circ}C$  to +85°C, typical values are at  $T_J = +25^{\circ}C$ , unless otherwise noted.)

PARAME	TER	SYMBOL	C	ONDITIONS	MIN	TYP	MAX	UNITS
Quiescent Curren	ts							
Battery Discharge (BAT, SW, SYS) in		I <sub>BQ_VBUS</sub>	V <sub>BAT</sub> = 4.5V, V <sub>VBUS</sub> < V <sub>VAC_UVLOZ</sub> , leakage between BAT and VBUS, BATFET off			0.1	1	μA
Battery Discharge (BAT) in Buck Mod		I <sub>BQ_HIZ_BOFF</sub>	V <sub>BAT</sub> = 4.5V, HIZ mod or no VBUS, I <sup>2</sup> C disa	le and BATFET_DIS = 1 bled, BATFET disabled		9	20	μΑ
Battery Discharge (BAT, SW, SYS)	Current	I <sub>BQ_HIZ_BON</sub>	V <sub>BAT</sub> = 4.5V, HIZ mod or no VBUS, I <sup>2</sup> C disa	le and BATFET_DIS = 0 bled, BATFET enabled		15	30	μΑ
			V <sub>VBUS</sub> = 5V, HIZ mode no battery	e and BATFET_DIS = 1,		20	40	
Input Supply Curre		I <sub>VBUS_HIZ</sub>	V <sub>VBUS</sub> = 12V, HIZ mod no battery	de and BATFET_DIS = 1,		40	65	- μA
(VBUS) in Buck Mo	ode		V <sub>VBUS</sub> = 12V, V <sub>VBUS</sub> >	V <sub>BAT</sub> , converter not switching		2.5	3.5	
		I <sub>VBUS</sub>	V <sub>BAT</sub> = 3.8V, I <sub>SYS</sub> = 0A V <sub>VBUS</sub> > V <sub>VAC_UVLOZ</sub> , co	A, V <sub>VBUS</sub> > V <sub>BAT</sub> , onverter switching, BATFET off		3		mA
Battery Discharge in Boost Mode	Current	I <sub>BOOST</sub>	V <sub>BAT</sub> = 4.2V, I <sub>VBUS</sub> = 0	A, converter switching		3		mA
BAT Pin, VAC Pin	and VBUS Pin	Power-Up						
VBUS Operating R	ange	$V_{VBUS\_OP}$	V <sub>VBUS</sub> rising		3.9		13.5	V
VBUS UVLO to Ha (with No Battery) S VAC Pin		V <sub>VAC_UVLOZ</sub>	V <sub>VAC</sub> rising, T <sub>J</sub> = +25°C			3.2	3.45	V
I <sup>2</sup> C Active Hysteres	sis	V <sub>VAC_UVLOZ_HYS</sub>	V <sub>VAC</sub> falling from above V <sub>VAC_UVLOZ</sub>			400		mV
V <sub>VAC</sub> Minimum (as Conditions) to Turr		V <sub>VAC_PRESENT</sub>	V <sub>VAC</sub> rising, T <sub>J</sub> = +25°C			3.4	3.7	V
V <sub>VAC</sub> Hysteresis (as Conditions) to Turr		V <sub>VAC_PRESENT_HYS</sub>	$V_{\text{VAC}}$ falling from above $V_{\text{VAC\_PRESENT}}$			400		mV
Sleep Mode Falling	Threshold	V <sub>SLEEP</sub>	$V_{VAC}$ - $V_{BAT}$ , $V_{VBUSMIN\_FALL} \le V_{BAT} \le V_{REG}$ , $V_{VAC}$ falling, $T_J = +25^{\circ}C$		20	50	80	mV
Sleep Mode Rising	Threshold	V <sub>SLEEPZ</sub>	$V_{VAC}$ - $V_{BAT}$ , $V_{VBUSMIN\_F}$ $T_J$ = +25°C	$F_{ALL} \le V_{BAT} \le V_{REG}, V_{VAC} \text{ rising},$	145	190	235	mV
VAC	6.5V Setting			OVP[1:0] = 01	6.25	6.5	6.75	
Over-Voltage	10.5V Setting	$V_{VAC\_OV\_RISE}$	V <sub>VAC</sub> rising	OVP[1:0] = 10	10.1	10.5	10.9	V
Rising Threshold	14V Setting			OVP[1:0] = 11	13.5	14	14.5	
VAC	6.5V Setting			OVP[1:0] = 01		100		
Over-Voltage	10.5V Setting	V <sub>VAC_OV_HYS</sub>		OVP[1:0] = 10		250		mV
Hysteresis	14V Setting			OVP[1:0] = 11		300		1
BAT Voltage to Have Active I <sup>2</sup> C (No Source on VBUS)		V <sub>BAT_UVLOZ</sub>	V <sub>BAT</sub> rising		2.65			V
BAT Depletion The	aabald	$V_{BAT\_DPL\_FALL}$	V <sub>BAT</sub> falling		2	2.25	2.5	V
BAT Depletion Threshold		V <sub>BAT_DPL_RISE</sub>	V <sub>BAT</sub> rising		2.25	2.5	2.75	V
BAT Depletion Rising Hysteresis		V <sub>BAT_DPL_HYS</sub>				260		mV
Bad Adapter Detection (Internal Current S	ink)	I <sub>BAD_SRC</sub>	V <sub>VBUS</sub> = 5V, sink curre	ent from VBUS to GND		30		mA
Bad Adapter Detection Voltage Drop) Falli	ng Threshold	V <sub>VBUSMIN_FALL</sub>	V <sub>VBUS</sub> falling		3.7	3.8	3.9	V
Bad Adapter Detection Voltage Drop) Hyst		V <sub>VBUSMIN_HYS</sub>				220		mV

 $(V_{VAC\_UVLOZ} < V_{VAC} < V_{VAC\_OV} \text{ and } V_{VAC} > V_{BAT} + V_{SLEEP}, T_J = -40^{\circ}\text{C} \text{ to } +85^{\circ}\text{C}, \text{ typical values are at } T_J = +25^{\circ}\text{C}, \text{ unless otherwise noted.})$ 

PARAMETER	SYMBOL	CONDITIONS			TYP	MAX	UNITS
Power Path Management		•					
System Regulation Voltage	$V_{SYS}$	V <sub>BAT</sub> = 4.4V, V <sub>BAT</sub> > V <sub>SYS_MIN</sub> , BATFET_DIS = 1			V <sub>BAT</sub> + 50mV		V
Minimum DC System Voltage Output	V <sub>SYS_MIN</sub>	V <sub>BAT</sub> < SYS_MIN[2:0] = BATFET_DIS = 1	= 101 (3.5V),	3.6	3.7		V
Maximum DC System Voltage Output	V <sub>SYS_MAX</sub>	V <sub>BAT</sub> ≤ 4.4V, V <sub>BAT</sub> > V <sub>SY</sub> BATFET_DIS = 1	<sub>VS_MIN</sub> = 3.5V,	4.38	4.45	4.52	V
Top Reverse Blocking MOSFET On-Resistance between VBUS and PMID - Q1	R <sub>ON_RBFET</sub>				16		mΩ
Top Switching MOSFET On-Resistance between PMID and SW - Q2	R <sub>ON_HSFET</sub>				22		mΩ
Bottom Switching MOSFET On-Resistance between SW and GND - Q3	R <sub>ON_LSFET</sub>				23		mΩ
BATFET Forward Voltage in Supplement Mode	$V_{\text{FWD}}$				25		mV
Battery Charger							
Charge Voltage Program Range	V <sub>BAT_REG_RANGE</sub>			3.856		4.624	V
Charge Voltage Step	V <sub>BAT_REG_STEP</sub>	Combined with VREG	_FT bits		8		mV
	V <sub>BAT_REG</sub>	VREG[4:0] = 01011 (4.208V)	T <sub>J</sub> = +25°C	4.192	4.208	4.224	
			T <sub>J</sub> = -40°C to +85°C	4.184		4.232	- - - - -
		VREG[4:0] = 01111	T <sub>J</sub> = +25°C	4.336	4.352	4.368	
Charge Voltage Setting		(4.352V)	T <sub>J</sub> = -40°C to +85°C	4.326		4.378	
		VREG[4:0] = 10001 (4.400V)	T <sub>J</sub> = +25°C	4.386	4.4	4.414	
			T <sub>J</sub> = -40°C to +85°C	4.374		4.426	
		$V_{BAT\_REG} = 4.208V$ or	T <sub>J</sub> = +25°C	-0.4		0.4	
Charge Voltage Setting Accuracy	$V_{BAT\_REG\_ACC}$	$V_{BAT\_REG} = 4.352V$ or $V_{BAT\_REG} = 4.400V$	T <sub>J</sub> = -40°C to +85°C	-0.6		0.6	%
Charge Current Regulation Range	I <sub>CHG_REG_RANGE</sub>	BATILES		0		1.26	Α
Charge Current Regulation Step	I <sub>CHG_REG_STEP</sub>				20		mA
			I <sub>CHG</sub> = 20mA		0.02		
			I <sub>CHG</sub> = 60mA	0.05	0.063	0.076	
		$V_{BAT} = 3.1V,$ $T_{J} = +25^{\circ}C$	I <sub>CHG</sub> = 240mA	0.215	0.24	0.265	
		11 - 125 0	I <sub>CHG</sub> = 720mA	0.68	0.72	0.76	
Charge Current Regulation			I <sub>CHG</sub> = 1.26A	1.16	1.26	1.36	1
Setting	CHG_REG		I <sub>CHG</sub> = 20mA		0.015		A
			I <sub>CHG</sub> = 60mA	0.035	0.055	0.075	
		$V_{BAT} = 3.8V,$ $T_{\perp} = +25^{\circ}C$	I <sub>CHG</sub> = 240mA	0.205	0.235	0.265	
		11 - 720 0	I <sub>CHG</sub> = 720mA	0.655	0.71	0.76	
			I <sub>CHG</sub> = 1.26A	1.105	1.23	1.335	
Pre-Charge Current Regulation Range	I <sub>PRECHG_RANGE</sub>	With 20mA/step	1	20		260	mA
Pre-Charge Current Regulation	I.	T - ±25°C	IPRECHG[3:0] = 0010 (60mA)	45	60	75	- A
Setting	I <sub>PRECHG</sub>	T <sub>J</sub> = +25°C	IPRECHG[3:0] = 0000 (20mA)	11	22	33	mA

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PARAMETER	SYMBOL	CONDITIONS			TYP	MAX	UNITS
Battery Charger							
Battery LOW Falling Threshold	V <sub>BATLOW_FALL</sub>	I <sub>CHG</sub> = 480mA		2.82	2.95	3.08	V
Battery LOW Rising Threshold	V <sub>BATLOW_RISE</sub>	Change from pre-charge	to fast charging	3.07	3.15	3.23	V
Termination Charge Current Regulation Range	I <sub>TERM_RANGE</sub>	With 20mA/step		20		320	mA
Termination Current Regulation		$V_{BAT\_REG} = 4.208V$ ,	ITERM[3:0] = 0010 (60mA)	47	58	69	
Setting	I <sub>TERM</sub>	T <sub>J</sub> = +25°C	ITERM[3:0] = 0000 (20mA)	11	18	25	mA
Dattam, Chart Valtaria	$V_{SHORT}$	V <sub>BAT</sub> falling, T <sub>J</sub> = +25°C		1.94	2	2.06	V
Battery Short Voltage	V <sub>SHORTZ</sub>	V <sub>BAT</sub> rising, T <sub>J</sub> = +25°C		2.15	2.2	2.25	
Battery Short Current	I <sub>SHORT</sub>	V <sub>BAT</sub> < V <sub>SHORTZ</sub>			30		mA
Recharge Threshold below		V falling	VRECHG = 0 (100mV)	90	115	140	\/
$V_{BAT\_REG}$	$V_{RECHG}$	V <sub>BAT</sub> falling	VRECHG = 1 (200mV)	200	225	250	- mV
System Discharge Load Current	I <sub>SYS_LOAD</sub>	V <sub>SYS</sub> = 4.2V			20		mA
BATFET MOSFET On-Resistance	R <sub>ON_BATFET</sub>	$V_{BAT}$ = 4.2V, measured fr $T_J$ = +25°C	om BAT pin to SYS pin,		10	18	mΩ
Input Voltage and Current Reg	ulation (DPM:	Dynamic Power Manage	ement)	•			•
Input Voltage Regulation Limit	V <sub>INDPM</sub>	VINDPM[3:0] = 0101	VINDPM_OS = 00 (4.4V)	4.32	4.4	4.48	- v
			VINDPM_OS = 01 (6.4V)	6.3	6.4	6.5	
			VINDPM_OS = 10 (8V)	7.86	8	8.14	
			VINDPM_OS = 11 (11V)	10.79	11	11.21	
Input Voltage Regulation Accuracy	V <sub>INDPM_ACC</sub>	T <sub>J</sub> = +25°C		-2		2	%
Input Voltage Regulation Limit Tracking VBAT	$V_{DPM\_VBAT}$	$V_{BAT} = 4V, V_{INDPM} = 3.9V, VDPM_BAT_TRACK[1:0]$		4.11	4.35	4.49	V
Input Current Regulation Limit Range	I <sub>INDPM</sub>	With 100mA/step		0.1		3.2	Α
range		V <sub>VBUS</sub> = 5V,	IINDPM[4:0] = 00100 (500mA)	400		630	
Input Current Regulation Limit	I <sub>INDPM</sub>	current pulled from SW,	IINDPM[4:0] = 01000 (900mA)	755		1015	mA
		T <sub>J</sub> = +25°C	IINDPM[4:0] = 01110 (1.5A)	1245		1535	
Input Current Limit during System Start-Up Sequence	I <sub>IN_START</sub>				250		mA
BAT Pin Over-Voltage Protection	on						
Battery Over-Voltage Threshold	V <sub>BATOVP_RISE</sub>	As percentage of	V <sub>BAT</sub> rising	102.8	103.8	104.8	%
Battery Over-voltage Threshold	V <sub>BATOVP_FALL</sub>	$V_{BAT\_REG}$ , $T_J = +25$ °C	V <sub>BAT</sub> falling	100.8	101.8	102.8	70
Thermal Regulation and Therm	al Shutdown						
Junction Temperature	Т	Temperature increasing	TREG = 1 (120°C)		120		- °C
Regulation Threshold	T <sub>JUNCTION_REG</sub>	remperature increasing	TREG = 0 (80°C)		80		
Thermal Shutdown Rising Temperature	T <sub>SHUT</sub>	Temperature increasing			150		°C
Thermal Shutdown Hysteresis	T <sub>SHUT_HYS</sub>				30		°C

 $(V_{VAC\_UVLOZ} < V_{VAC} < V_{VAC\_OV} \text{ and } V_{VAC} > V_{BAT} + V_{SLEEP}, T_J = -40^{\circ}\text{C} \text{ to } +85^{\circ}\text{C}, \text{ typical values are at } T_J = +25^{\circ}\text{C}, \text{ unless otherwise noted.})$ 

noted.)  PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
JEITA Thermistor Comparator (Buck	Mode)						
T1 (0°C) Threshold Voltage on TS Pin	$V_{T1}$	Charge suspends if temperature (T < T1), as percentage of V <sub>REGN</sub>	Charge suspends if temperature T is below T1 (T < T1), as percentage of V <sub>REGN</sub>		73.2	73.6	%
V <sub>T1</sub> Falling		As percentage of V <sub>REGN</sub>		71.2	71.6	72	
T2 (10°C) Threshold Voltage on TS Pin	$V_{T2}$	Charge sets to $I_{\text{CHG}}/2$ and the low $V_{\text{REG}}$ if T1 < T < T2, as percentag		67.6	68	68.4	%
V <sub>T2</sub> Falling		As percentage of V <sub>REGN</sub>		66.2	66.6	67	
V <sub>T3</sub> Rising		As percentage of V <sub>REGN</sub>		45.5	45.9	46.3	
T3 (45°C) Threshold Voltage on TS Pin	$V_{T3}$	Charge sets to the lower of 4.1V if T3 < T < T4, as percentage of \		44.1	44.5	44.9	%
V <sub>T4</sub> Rising	V	As percentage of V <sub>REGN</sub>		35.1	35.5	35.9	%
T4 (60°C) Threshold Voltage on TS Pin	$V_{T4}$	Charge suspends if T > T4, as pe	rcentage of V <sub>REGN</sub>	33.8	34.2	34.6	70
Cold or Hot Thermistor Comparator (	(Boost Mode)	 					_
Cold Temperature Threshold (TS Pin Voltage Rising Threshold)	$V_{BCOLD}$	As percentage of V <sub>REGN</sub> (approx.	-20°C w/ 103AT)	79.5	80	80.5	- %
TS Voltage Falling (Exit Cold Range)	50025	As percentage of V <sub>REGN</sub>		78.5	79	79.5	
Hot Temperature Threshold (TS Pin Voltage Falling Threshold)	$V_{BHOT}$	As percentage of V <sub>REGN</sub> (approx.	As percentage of V <sub>REGN</sub> (approx. 60°C w/ 103AT)		34.5	35	%
TS Voltage Rising (Exit Hot Range)		As percentage of V <sub>REGN</sub>		30.7	31.2	31.7	
Charge Over-Current Comparator (C	ycle-by-Cycle	e)					
HSFET Cycle-by-Cycle Over-Current Threshold	I <sub>HSFET_OCP</sub>	T <sub>J</sub> = +25°C		6.4		9.3	Α
System Overload Threshold	I <sub>BATFET_OCP</sub>	T <sub>J</sub> = +25°C		5.3			Α
Charge Under-Current Comparator (	Cycle-by-Cyc	le)					
LSFET Under-Current Falling Threshold	I <sub>LSFET_UCP</sub>	Change rectifier from synchronou non-synchronous mode	is mode to		180		mA
PWM							
PWM Switching Frequency	f <sub>SW</sub>	Oscillator frequency, T <sub>J</sub> = +25°C	Buck mode	1380	1500	1620	kHz
r vvivi Switching Frequency	ISW	Oscillator frequency, 1, = +25 C	Boost mode	1380	1500	1620	NI IZ
Maximum PWM Duty Cycle (1)	$D_{MAX}$				99		%
Boost Mode Operation							
Boost Mode Regulation Voltage	$V_{BST\_REG}$	V <sub>BAT</sub> = 3.8V, I <sub>PMID</sub> = 0A, BOOSTV	[1:0] = 01 (5V)	4.88	5	5.12	V
		V <sub>BAT</sub> falling, MIN_BAT_SEL = 0		2.92	3	3.08	
Exit Boost Mode Due to Low Battery	M	V <sub>BAT</sub> rising, MIN_BAT_SEL = 0		3.08	3.2	3.32	V
Voltage	V <sub>BATLOW_BST</sub>	V <sub>BAT</sub> falling, MIN_BAT_SEL = 1		2.52	2.6	2.68	
		V <sub>BAT</sub> rising, MIN_BAT_SEL = 1		2.68	2.8	2.92	
Boost Over-Voltage Threshold	V <sub>BST_OVP</sub>	Rising threshold		5.85	6	6.15	V
HSFET Under-Current Falling Threshold	I <sub>BST_HSZCP</sub>	Change rectifier from synchronou non-synchronous mode	is mode to		320		mA

 $(V_{VAC\_UVLOZ} < V_{VAC} < V_{VAC\_OV} \text{ and } V_{VAC} > V_{BAT} + V_{SLEEP}, T_J = -40^{\circ}\text{C} \text{ to } +85^{\circ}\text{C}, \text{ typical values are at } T_J = +25^{\circ}\text{C}, \text{ unless otherwise noted.})$ 

PARAMETER		SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	
REGN LDO								
RECNI DO Output Val	togo	$V_{REGN}$	V <sub>VBUS</sub> = 9V, I <sub>REGN</sub> = 40mA	4.3	4.7	5.1	\/	
REGN LDO Output Voltage		V REGN	$V_{VBUS} = 5V$ , $I_{REGN} = 20mA$	4.75	4.85	5	- V	
Logic I/O Pin Charact	Logic I/O Pin Characteristics (nCE, PSEL, DCEN, SCL, SDA and nINT)							
Input Low Threshold	nCE	V <sub>IL</sub>				0.4	V	
Input High Threshold	IICE	V <sub>IH</sub>		1.3			V	
Input Low Threshold	PSEL, SCL,	V <sub>IL</sub>				0.4	V	
Input High Threshold	SDA, nINT	V <sub>IH</sub>		1.3			V	
High-Level Leakage Current		I <sub>BIAS</sub>	Pull up rail 1.8V		0.1	1	μA	
Logic I/O Pin Characteristics (PMID_GD, STAT) – Open-Drain								
Low-Level Output Voltage		V <sub>OL</sub>				0.2	V	

#### NOTE:

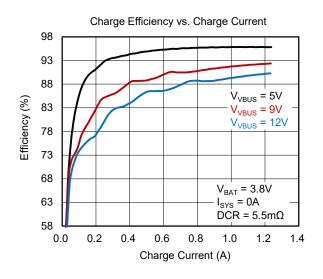
1. Guaranteed by design. Not production tested.

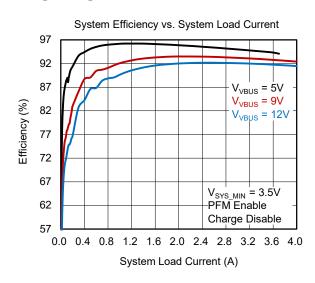
### **TIMING REQUIREMENTS**

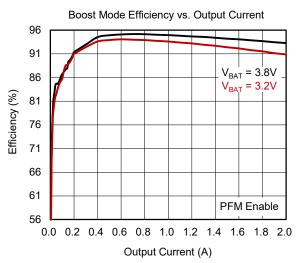
 $(T_J = +25^{\circ}C, \text{ unless otherwise noted.})$ 

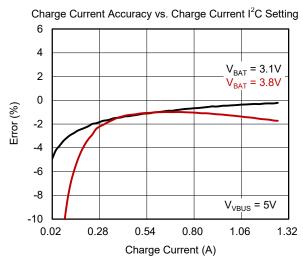
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
V <sub>VBUS</sub> /V <sub>BAT</sub> Power-Up						
VBUS OVP Reaction Time	t <sub>ACOV</sub>	V <sub>VBUS</sub> rising above ACOV threshold to turn off Q2		0.1		μs
Wait Window for Bad Adapter Detection	t <sub>BADSRC</sub>			30		ms
Battery Charger						
Deglitch Time for Charge Termination	t <sub>TERM_DGL</sub>			30		ms
Deglitch Time for Recharge	t <sub>RECHG_DGL</sub>			30		ms
System Over-Current Deglitch Time to Turn off Q4	t <sub>SYSOVLD_DGL</sub>			112		μs
Battery Over-Voltage Deglitch Time to Disable Charge	t <sub>BATOVP</sub>			1		μs
Turisal Change Cafate Timesa Dange		CHG_TIMER = 0	18 20 24		-	
Typical Charge Safety Timer Range	t <sub>SAFETY</sub>	CHG_TIMER = 1	10	11.5	13	h
Typical Top-off Timer Range	t <sub>TOP_OFF</sub>	TOPOFF_TIMER[1:0] = 10 (30min)	30	35	40	min
nQON Timing and Ship Mode Timing						
nQON Negative Pulse Low Pulse Width to Turn on BATFET and Exit Ship Mode	t <sub>SHIPMODE</sub>		0.8	1	1.2	s
nQON Low Time to Reset BATFET	t <sub>QON_RST</sub>		8	10	12	s
BATFET off Time during Full System Reset	t <sub>BATFET_RST</sub>		285	320	355	ms
Wait Delay for Entering Ship Mode	t <sub>SM_DLY</sub>		11.5	12.5	13.5	s
Digital Clock and Watchdog Timer						
Watchdog Reset Time	t <sub>WDT</sub>	WATCHDOG[1:0] = 01, REGN LDO disabled		40.9		s
Digital Clock Frequency in Low Power	f <sub>LPDIG</sub>	REGN LDO disabled		31		kHz
Digital Clock Frequency	f <sub>DIG</sub>	REGN LDO enabled		500		kHz
I <sup>2</sup> C Interface						
SCL Clock Frequency	f <sub>SCL</sub>			400		kHz

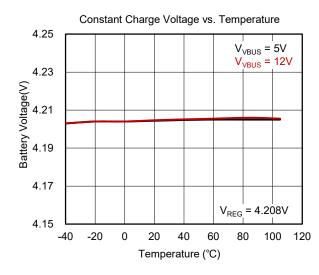
#### TYPICAL PERFORMANCE CHARACTERISTICS

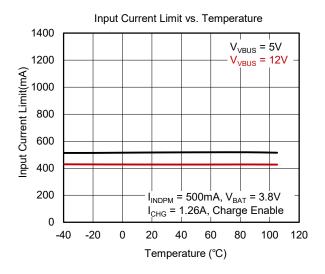




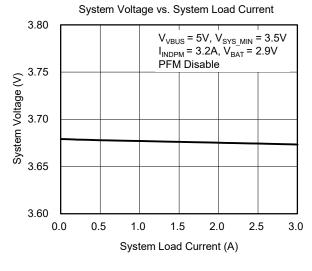


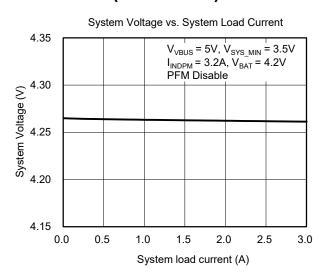


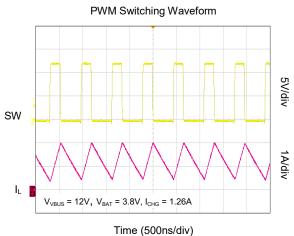


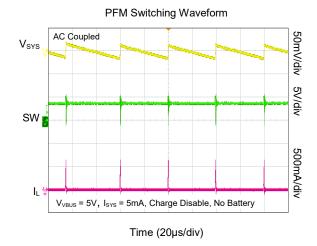


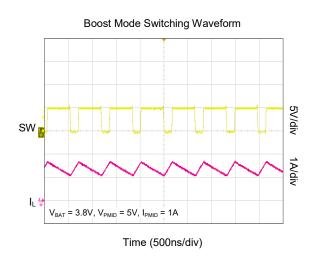
### **TYPICAL PERFORMANCE CHARACTERISTICS (continued)**

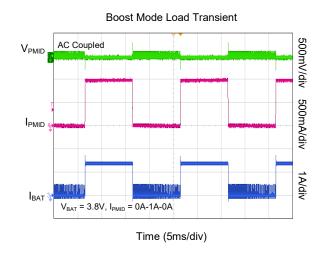




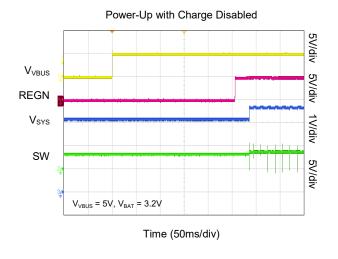


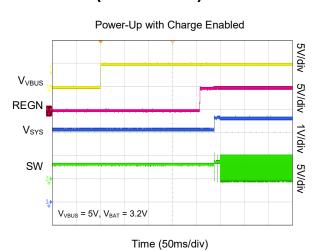


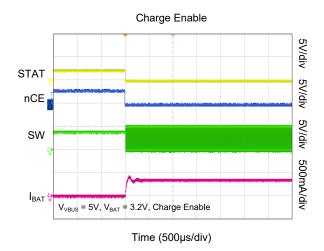


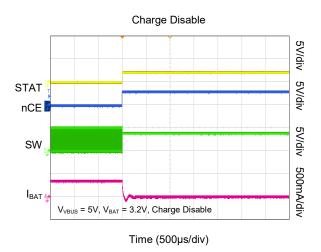


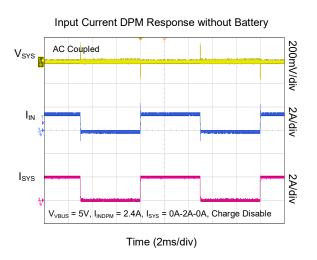
### **TYPICAL PERFORMANCE CHARACTERISTICS (continued)**

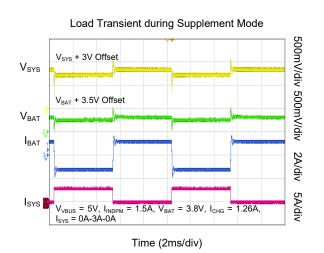




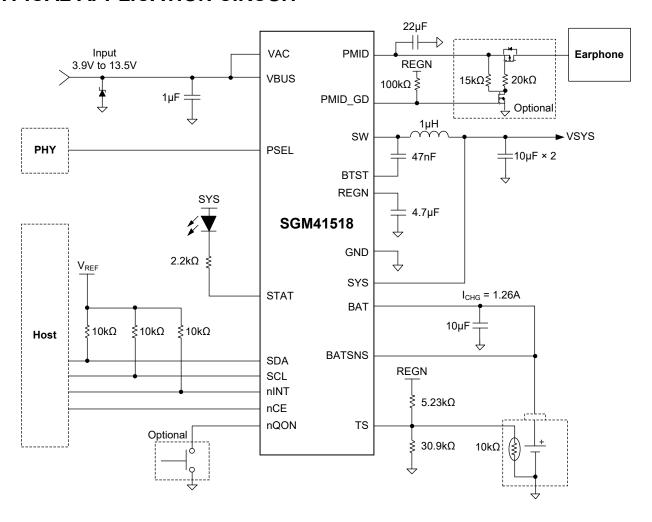








#### TYPICAL APPLICATION CIRCUIT



**Figure 1. Typical Application Circuit** 

#### **FUNCTIONAL BLOCK DIAGRAM**

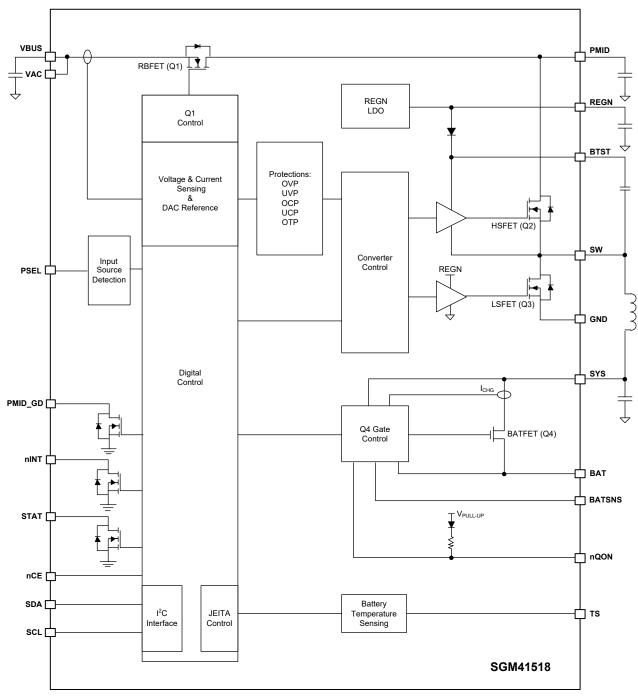


Figure 2. Block Diagram

#### **DETAILED DESCRIPTION**

The SGM41518 is a power management and charger device for applications such as wearables and earphones with single-cell Li-lon or Li-polymer batteries. The SGM41518 can accommodate a wide range of input sources including USB, wall adapter and car chargers. It is optimized for 5V input (USB voltage) but is capable to operate with input voltages from 3.9V to 13.5V. It also supports JEITA profile for battery charging safety at high or low temperatures. Automatic power path selection to power the system (SYS) from the input source (VBUS), battery (BAT), or both, is another feature of the device. Battery charge current is programmable and can reach to a maximum of 1.26A (charge).

The device may operate in several different modes:

In HIZ mode, the reverse blocking FET (Q1), internal REGN LDO, converter switches and some other parts of the internal circuit remain off to save the battery while it is supplying DC power to the system through BATFET.

In the sleep mode, the switching is stopped. The charger goes to the sleep mode when the input source voltage ( $V_{VAC}$ ) is not high enough for charging the battery. In other words,  $V_{VAC}$  is smaller than  $V_{BAT}$  +  $V_{SLEEP}$  (where  $V_{SLEEP}$  is a small threshold) and Buck converter is not able to charge, even at its maximum duty cycle. The Boost may also go to the sleep mode if similar issue happens in the reverse direction (when  $V_{VAC}$  is almost equal or smaller than  $V_{BAT}$ ).

In supplement mode, the input source power is not enough to supply system demanded power and the battery assists by discharging to the system in parallel, and providing the deficit.

#### Power-On Reset (POR)

The internal circuit of the device is powered from the greater voltage between  $V_{VBUS}$  and  $V_{BAT}.$  When the voltage of the selected source goes above its UVLO level ( $V_{VBUS} > V_{VAC\_UVLOZ}$  or  $V_{BAT} > V_{BAT\_UVLOZ}$ ), a POR happens and activates the sleep comparator, battery depletion comparator and BATFET driver. Upon activation, the  $I^2C$  interface will also be ready for communication and all registers reset to their default values.

### Power-Up from Battery Only (No Input Source)

When only the battery is presented as a source and its voltage is above depletion threshold ( $V_{BAT\_DPL\_RISE}$ ), the BATFET turns on and connects the battery to the system. The quiescent current is minimum because the REGN LDO remains off. Conduction losses are also low due to small  $R_{DSON}$  of BATFET. Low losses help to extend the battery run time.

The discharge current through BATFET is continuously monitored. In the supplement mode, if a system overload (or short) occurs ( $I_{BAT} > I_{BATFET\_OCP}$ ), the BATFET is turned off immediately and BATFET\_DIS bit is set to 1. The BATFET will not enable until the input source is applied or one of the BATFET Enable Mode (Exit Ship Mode) methods (explained later) is used to activate the BATFET.

#### **Power-Up Process from the Input Source**

Upon connection of an input source (VBUS), its voltage sensed from VAC pin is checked to turn on the internal REGN LDO regulator and the bias circuits (no matter whether the battery is present or not). The input current limit is determined and set before the Buck converter is started. The sequences of actions when VBUS as input source is powered up are:

- 1. REGN LDO power-up.
- 2. Poor power source detection (qualification).
- **3. Input power source type detection.** (Based on PSEL input. It is used to set the default input current limit (IINDPM[4:0]).)
- 4. Setting of the input voltage limit threshold (VINDPM threshold).
- 5. DC/DC converter power-up.

Details of the power-up steps are explained in the following sections.

#### **REGN LDO Power-Up**

The REGN low dropout regulator powers the internal bias circuits, HSFET and LSFET gate drivers and TS rail (thermistor pin). The STAT pin can also be pulled up to REGN. The REGN enables when the following 2 conditions are satisfied and remain valid for a 220ms delay time, otherwise the device stays in high impedance mode (HIZ) with REGN LDO off.

- 1. V<sub>VAC</sub> > V<sub>VAC</sub> PRESENT.
- 2.  $V_{VAC}$  >  $V_{BAT}$  +  $V_{SLEEPZ}$  (in Buck mode) or  $V_{VBUS}$  <  $V_{BAT}$  +  $V_{SLEEP}$  (in Boost mode).

In HIZ state, the quiescent current drawn from VBUS is very small (less than  $I_{VBUS\_HIZ}$ ). System is only powered by the battery in HIZ mode.

#### **Poor Power Source Detection (Qualification)**

When REGN LDO is powered, the input source (adaptor) is checked for its type and current capacity. To start the Buck converter, the input (VBUS) must meet the following conditions:

- 1. V<sub>VBUS</sub> < V<sub>VAC</sub> ov.
- 2.  $V_{VBUS} > V_{VBUS\_MIN}$  during  $t_{BADSRC}$  test period (30ms TYP) in which the  $I_{BAD\ SRC}$  (30mA TYP) current is pulled from VBUS.

If the test is failed, the conditions are repeatedly checked every 2 seconds. As soon as the input source passes qualification, the VBUS\_GD bit in status register is set to 1 and a pulse is sent to the nINT pin to inform the host. Type detection will start as next step.

#### **Input Power Source Type Detection**

The input source detection will run through the PSEL pin while REGN LDO is powered and after the VBUS\_GD bit is set. The input current limit of the SGM41518 is set based on the state of PSEL pin. When the input source type detection is completed, the PMID\_GD pin is asserted to high and the PG\_STAT bit is set to 1. A pulse is sent to nINT pin to inform the host when the input source type detection is completed. Some registers and pins are also updated as detailed below:

- 1. Input current limit register (the value in the IINDPM[4:0]) is changed to set current limit.
- 2. PG\_STAT (power good) bit is set.
- 3. VBUS\_STAT[2:0] register is updated to indicate USB or adaptor input source types.

The input current is always limited by the IINDPM[4:0] register and the limit can be updated by the host if needed.

#### Input Current Limit by PSEL

PSEL pin interfaces with USB physical layer (PHY) for input current limit setting. The USB PHY device output is used to detect if the input is a USB host or a charging port. In the host-control mode, the host must enable IINDET\_EN bit for reading the PSEL value and updating the IINDPM[4:0]. In the default mode, IINDPM[4:0] is updated automatically by PSEL value in real-time as given in Table 1.

**Table 1. Input Current Limit Setting from PSEL** 

Input Detection	PSEL Pin	Input Current Limit (I <sub>LIM</sub> )	VBUS_STAT[2:0]
USB Host SDP	High	500mA	001
Adapter	Low	2400mA	011

### Setting of the Input Voltage Limit Threshold (VINDPM Threshold)

A wide voltage range (3.9V to 5.4V, 5.9V to 9V, 10.5V to 12V) is supported for the input voltage limit setting in VINDPM[3:0] and VINDPM\_OS[1:0]. 4.5V is the default for USB.

The device supports dynamic tracking of the battery voltage (VINDPM). VDPM\_BAT\_TRACK[1:0] bits can be used to enable tracking (00 to disable tracking) and set the tracking offset value. When the tracking is enabled, the input voltage limit will be set to the larger value between the VINDPM[3:0] and  $V_{BAT}$  + VDPM\_BAT\_TRACK[1:0]. The VDPM\_BAT\_TRACK[1:0] tracking offset can be set to 200mV, 250mV or 300mV. And this function only takes effect when VINDPM OS[1:0] = 00.

#### **DC/DC Converter Power-Up**

The 1.5MHz switching converter composed of LSFET and HSFET is enabled, which can start switching when the input current limit is set. Converter is initiated with a soft-start when the system voltage is ramped up. If SYS voltage is less than 2.2V, the input current is limited to 250mA or IINDPM[4:0], whichever is smaller, otherwise the limit is set to IINDPM[4:0].

The BATFET remains on to charge the battery if the battery charging function is enabled, otherwise BATFET turns off.

When converter operates for battery charging, it acts as an efficient, fixed frequency synchronous Buck converter regardless of the input/output voltages and currents. However, it is capable to switch to PFM mode at light load when charging is disabled or when the detected battery voltage is less than minimum system voltage setting. PFM operation can be enabled or prevented in either Buck or Boost mode using the PFM DIS bit.



#### **Boost Mode**

The SGM41518 supports Boost mode. When a load device is connected to the USB port, the converter can operate as a step-up synchronous converter (Boost mode) with 1.5MHz switching frequency to supply power from the battery to that load. Converter will be set to Boost mode if at least 30ms is passed from enabling this mode (BST\_CONFIG bit = 1) and the following conditions are satisfied:

- 1.  $V_{BAT} > V_{BATLOW BST}$ .
- 2.  $V_{VBUS} < V_{BAT} + V_{SLEEP}$  (in sleep mode).
- 3. Acceptable voltage range at TS pin ( $V_{BHOT} < V_{TS} < V_{BCOLD}$ ).

The output voltage is set to  $V_{PMID}$  = 5V and is maintained as long as  $V_{BAT}$  is above  $V_{BATLOW\_BST}$ . The VBUS\_STAT[2:0] status register bits are set to 111 in Boost mode.

To minimize the output overshoot in Boost mode, the device starts with PFM first and then switches to PWM. As stated before, PFM can be avoided by using PFM\_DIS bit in Buck and Boost modes.

The SGM41518 keeps the Q1 FET off in Boost mode. By setting both the BST\_CONFIG bit and the CHG\_CONFIG bit to 1 during adapter insertion or removal, the charger will automatically transition between charging mode and Boost mode. The device is in charge mode when the adapter is plugged in and the conditions to start a new charge cycle are valid. If the adapter is removed and the Boost enable conditions are active, the device automatically transitions to Boost mode to power accessories connected to the PMID.

### Host Mode and Default Mode Operation with Watchdog Timer

After a power-on reset, the device starts in default mode (standalone) with all registers reset as if the watchdog timer is expired. When the host is in sleep mode or there is no host, the device stays in the default mode in which the SGM41518 operates like an autonomous charger. The battery is charged for 11.5 hours (default value for the fast charging safety timer). Then the charge stops while Buck converter continues to operate to power the system load. In this mode, WATCHDOG FAULT bit is high.

Most of the flexibility features of the SGM41518 become available in the host mode when the device is controlled by a host with I<sup>2</sup>C. By setting the WD RST bit to 1, the charger mode changes from default mode to host mode. In this mode, the WATCHDOG FAULT bit is low and all device parameters can be programmed by the host. To prevent the device watchdog from reset that results in going back to default mode, the host must disable the watchdog timer by setting WATCHDOG[1:0] = 00, or it must consistently reset the watchdog timer before expiry by writing 1 to WD RST to prevent WATCHDOG FAULT bit from being set. Every time a 1 is written to the WD RST, the watchdog timer will restart counting. Therefore, it should be reset again before overflow (expiry) to keep the device in the host mode. If the watchdog timer expires (WATCHDOG FAULT bit = 1), the device returns to default mode and all registers are reset to their default values except for EN\_ICHG\_MON[1:0], IINDPM[4:0], PFM\_DIS, SYS\_MIN[2:0], MIN BAT SEL, Q1 FULLON, OVP[1:0], BOOSTV[1:0], VINDPM[3:0], VDPM\_BAT\_TRACK[1:0], BATFET DIS, BATFET\_DLY, VINDPM\_INT\_MASK, IINDPM\_INT\_MASK, REG RST and VINDPM OS[1:0] bits that keep their values unchanged.

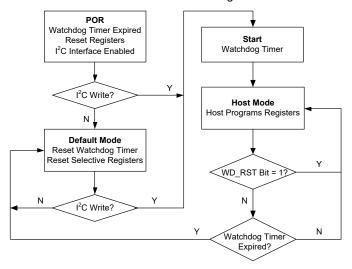


Figure 3. Watchdog Timer Flow Chart



#### **Battery Charging Management**

The SGM41518 is designed for charging single-cell Li-lon or Li-poly batteries with a charge current up to 1.26A (MAX). The battery connection switch (BATFET) is in the charge or discharge current path features low on-resistance ( $10m\Omega$  TYP) to allow high efficiency and low voltage drop.

#### **Charging Cycle in Autonomous Mode**

Charging is enabled if CHG\_CONFIG = 1 and nCE pin is pulled low. In default mode, the SGM41518 runs a charge cycle with the default parameters itemized in Table 2. At any moment, the device can be controlled by changing to the host mode.

**Table 2. Charging Parameter Default Setting** 

Default Mode	SGM41518
Charging Voltage (V <sub>REG</sub> )	4.208V
Charging Current (I <sub>CHG_REG</sub> )	340mA
Pre-Charge Current (I <sub>PRECHG</sub> )	40mA
Termination Current (I <sub>TERM</sub> )	60mA
Temperature Profile	JEITA
Safety Timer	11.5h

#### Start a New Charging Cycle

If the converter can start switching and all the following conditions are satisfied, a new charge cycle starts:

- NTC temperature fault is not asserted (TS pin).
- · Safety timer fault is not asserted.
- BATFET is not forced off. (BATFET DIS bit = 0).
- Charging enabled (3 conditions: CHG\_CONFIG bit = 1, ICHG[5:0] register is not 0mA and nCE pin is low).
- $\bullet$  Battery voltage is below the programmed full charge level (V $_{\text{REG}}$  ).

A new charge cycle starts automatically if battery voltage falls below the recharge threshold level (V<sub>REG</sub> - 100mV or V<sub>REG</sub> - 200mV configured by VRECHG bit). Also, if the charge cycle is completed, a new charging cycle can be initiated by toggling of the nCE pin or CHG\_CONFIG bit.

Normally a charge cycle terminates when the charge voltage is above the recharge threshold level and the charging current falls below the termination threshold if the device is not in thermal regulation or Dynamic Power Management (DPM) mode.

#### **Charge Status Report**

STAT is an open-drain output pin that reports the status of charge and can drive an LED for indication: a low indicates charging is in progress, a high shows charging is completed or disabled and alternating low/high (blinking) show a charging fault. The STAT may be disabled (keep the open-drain switch off) by setting EN\_ICHG\_MON[1:0] = 11.

The CHRG\_STAT[1:0] status register reports the present charging phase and status by two bits: 00 = charging disabled, 01 = in pre-charge, 10 = in fast charging (constant current mode or constant voltage mode) and 11 = charging completed.

A negative pulse is sent on nINT pin to inform the host when a charging cycle is completed.

In addition, the output status of STAT pin can be set by STAT\_SET[1:0] bits, 00 = LED off (HIZ), 01 = LED on (low), 10 = LED blinking at 1s on 1s off, 11 = LED blinking at 1s on 3s off. This two bits only take effect when EN\_ICHG\_MON[1:0] = 01.

#### **Battery Charging Profile**

The SGM41518 features a full battery charging profile with five phases. In the beginning of the cycle, the battery voltage ( $V_{BAT}$ ) is tested and appropriate current and voltage regulation levels are selected as shown in Table 3. Depending on the detected status of the battery, the proper phase is selected to start or for continuation of the charging cycle. The phases are trickle charge ( $V_{BAT}$  < 2.2V), pre-charge and fast-charge (constant current and constant voltage).

Table 3. Charging Current Setting Based on VBAT

V <sub>BAT</sub> Voltage	Selected Charging Current	Default Value in the Register	CHRG_STAT[1:0]	
< 2.2V	I <sub>SHORT</sub>	30mA	01	
2.2V to 3.15V	I <sub>PRECHG</sub>	40mA	01	
> 3.15V	I <sub>CHG</sub>	340mA	10	

Note that in the DPM or thermal regulation modes, normal charging functions are temporarily modified: The charge current will be less than the value in the register; termination is disabled, and the charging safety timer is slowed down by counting at half clock rate.

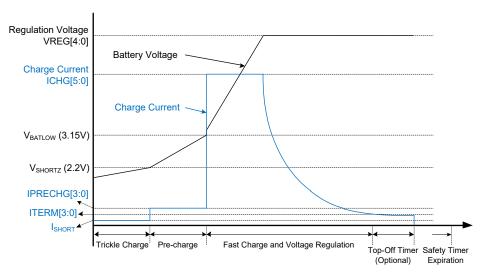


Figure 4. Battery Charging Profile

#### **Charge Termination**

A charge cycle is terminated when the battery voltage is higher than the recharge threshold and the charge current falls below the programmed termination current. Unless there is a high power demand for system and it needs to operate in supplement mode, the BATFET turns off at the end of the charge cycle. Even after termination, the Buck converter operates continuously to supply the system.

CHRG\_STAT[1:0] is set to 11 and a negative pulse is sent to nINT pin after termination.

If the charger is regulating input current, input voltage or junction temperature instead of charge current, termination will be temporarily prevented. EN\_TERM bit is termination control bit and can be set to 0 to disable termination before it happens.

At low termination currents (60mA TYP), the offset in the internal comparator may give rise to a higher (+5mA to +10mA) actual termination current. A delay in termination can be added (optional) as a compensation for comparator offset using a programmable top-off timer. During the delay, constant voltage charge phase continues and gives the falling charge current a chance to drop closer to the programmed value. The top-off delay timer has the same restrictions of the safety timer. As an example, if under some conditions the

safety timer is suspended, the top-off timer will also be suspended or if the safety timer is slowed down, the termination timer will also be slowed down. The TOPOFF\_ACTIVE bit reports the active/not active status of the top-off timer. The CHRG\_STAT[1:0] and TOPOFF\_ACTIVE bits can be read to find status of the termination.

Any of the following events resets the top-off timer:

- 1. Disable to enable transition of nCE (charge enable).
- 2. A low to high change in the status of termination.
- 3. Set REG RST bit to 1.

The setting of the top-off timer is applied at the time of termination detection and unless a new charge cycle is started, modifying the top-off timer parameters after termination has no effect. A negative pulse is sent to nINT when top-off timer is started or ended.

#### **Temperature Qualification**

The charging current and voltage of the battery must be limited when battery is cold or hot. A thermistor input for battery temperature monitoring is included in the device that can protect the battery based on JEITA guidelines.



#### **Compliance with JEITA Guideline**

JEITA guideline (April 20, 2007 release) is implemented in the device for safe charging of the Li-Ion battery. JEITA highlights the considerations and limits that should to be considered for charging at cold or hot battery temperatures. High charge current and voltage must be avoided outside normal operating temperatures (typically 0 °C and 60 °C). This functionality can be disabled if not needed. Four temperature levels are defined by JEITA from T1 (minimum) to T4 (maximum). Outside this range, charging should be stopped. The corresponding voltages sensed by NTC are named  $V_{T1}$  to  $V_{T4}$ . Due to the sensor negative resistance, a higher temperature results in a lower voltage on TS pin. The battery cool range is between T1 and T2, and the warm range is between T3 and T4. Charge must be limited in the cool and warm ranges.

One of the conditions for starting a charge cycle is having the TS voltage within  $V_{T1}$  to  $V_{T4}$  window limits. If during the charge, battery gets too cold or too hot and TS voltage exceeds the T1 - T4 limits, charging is suspended (zero charge current) and the controller waits for the battery temperature to come back within the T1 to T4 window.

JEITA recommends reducing charge current to 1/2 of fast charging current or lower at cool temperatures (T1 - T2). For warmer temperature (within T3 - T4 range), charge voltage is recommended to be kept below 4.1V.

The SGM41518 exceeds the JEITA requirement by its flexible charge parameter settings. At warm temperature range (T3 - T4), the charge voltage is set to the lower of  $V_{REG}$  and 4.1V when JEITA\_VSET\_H = 0, the charge voltage is set to  $V_{REG}$  when JEITA\_VSET\_H = 1, and the charge current can be reduced down to 0%, 20% or 50% of fast charging current by

the JEITA\_ISET\_H[1:0] bits. At cool temperatures (T1 - T2), the current setting can be reduced down to 50% or 20% of fast charging current selectable by the JEITA\_ISET\_L bit when JEITA\_ISET\_L\_EN = 1, and the charge voltage is set to  $V_{REG}$  when JEITA\_VSET\_L = 0, the charge voltage is set to the lower of  $V_{REG}$  and 4.1V when JEITA\_VSET\_L = 1. Additional, the cool threshold T2 and warm threshold T3 can be changed through JEITA\_VT2 [1:0] and JEITA\_VT3 [1:0], and the charge current can be disabled by setting JEITA\_ISET\_L\_EN = 0.

A 103AT-2 type thermistor is recommended to use with the SGM41518. Other thermistors may be used and bias network (see Figure 5) can be calculated based on the following equations:

$$R_{T2} = \frac{R_{THCOLD} \times R_{THHOT} \times \left(\frac{1}{V_{T1}} - \frac{1}{V_{T4}}\right)}{R_{THHOT} \times \left(\frac{1}{V_{T4}} - 1\right) - R_{THCOLD} \times \left(\frac{1}{V_{T1}} - 1\right)}$$
(1)

$$R_{T1} = \frac{\left(\frac{1}{V_{T1}} - 1\right)}{\left(\frac{1}{R_{T2}}\right) + \left(\frac{1}{R_{THCOLD}}\right)}$$
(2)

where  $V_{T1}$  and  $V_{T4}$  are  $T_{COLD}$  and  $T_{HOT}$  threshold voltage on TS pin as percentage to  $V_{REGN},\ R_{THCOLD}$  and  $R_{THHOT}$  are thermistor resistances (R\_{TH}) at desired T1 (Cold) and T4 (Hot) temperatures. Select  $T_{COLD}=0^{\circ}C$  and  $T_{HOT}=60^{\circ}C$  for Li-lon or Li-polymer batteries. For a 103AT-2 type thermistor  $R_{THCOLD}=27.28k\Omega$  and  $R_{THHOT}=3.02k\Omega,$  the calculation results are:  $R_{T1}=5.29k\Omega$  and  $R_{T2}=30.72k\Omega.$  The standard value is  $5.23k\Omega$  for  $R_{T1}$  and  $30.9k\Omega$  for  $R_{T2}.$ 

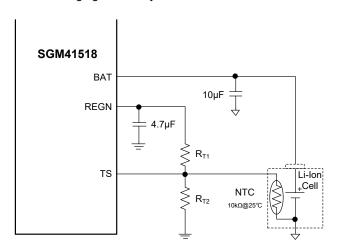


Figure 5. Battery Thermistor Connection and Bias Network

### Boost Mode Temperature Monitoring (Battery Discharge)

The device is capable to monitor the battery temperature for safety during the Boost mode. The temperature must remain within the  $V_{BCOLD}$  to  $V_{BHOT}$  thresholds, otherwise the Boost mode will be suspended and VBUS\_STAT[2:0] bits are set to 000. Moreover, NTC\_FAULT[2:0] register is updated to report Boost mode cold or hot condition. Once the temperature returns within the window, the Boost mode is resumed and NTC FAULT[2:0] register is cleared to 000 (normal).

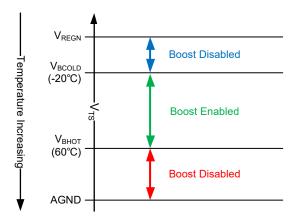


Figure 6. TS Pin Thermistor Temperature Window Settings in Boost Mode

#### **Safety Timer**

Abnormal battery conditions may result in prolonged charge cycles. An internal safety timer is considered to stop charging in such conditions. If the safety time is expired, CHRG\_FAULT[1:0] bits are set to 11 and a negative pulse is sent to nINT pin. By default, the charge time limit is 2 hours if the battery voltage does not rise above V<sub>BATLOW</sub> threshold. And it is 11.5 hours if it goes above V<sub>BATLOW</sub>. This feature is optional and can be disabled by clearing EN\_TIMER bit. The 11.5 hours limit can also be changed to 20 hours by clearing CHG\_TIMER bit.

The safety timer counts at half clock rate when charger is running under input voltage regulation, input current regulation, JEITA cool or thermal regulation, because in these conditions, the actual charge current is likely to be less than the register setting. As an example, if the safety timer is set to 11.5 hours and the charger is regulating the input current (IINDPM\_STAT bit = 1) in the whole charging cycle, the actual safety time will be 23 hours. Clearing the TMR2X\_EN bit will disable the half clock rate feature.

The safety timer is paused if a fault occurs and charging is suspended. It will resume once the fault condition is removed. If charging cycle is stopped by a restart or by toggling nCE pin or CHG\_CONFIG bit, the timer resets and restarts a new timing.

#### Narrow Voltage DC (NVDC) Design in SGM41518

The SGM41518 features an NVDC design using the BATFET that connects the system and battery. By using the linear region of the BATFET, the charger regulates the system bus voltage (SYS pin) above the minimum setting using Buck converter even if the battery voltage is very low. MOSFET linear mode allows for the large voltage difference between SYS and BAT pins to appear as  $V_{DS}$  across the switch while conducting and charging battery. SYS\_MIN[2:0] register sets the minimum system voltage (default 3.5V). If the system is in minimum system voltage regulation, VSYS\_STAT bit is set.

The BATFET operates in linear region when the battery voltage is below the minimum system voltage setting. The system voltage is regulated to 180mV (TYP) above the minimum system voltage setting. The battery gradually gets charged and its voltage rises above the minimum system voltage and lets BATFET to change from linear mode to fully turned-on switch such that the voltage difference between the system and battery is the small V<sub>DS</sub> of fully on BATFET.

The system voltage is always regulated to 50mV (TYP) above the battery voltage if:

- 1. The charging is terminated.
- 2. Charging is disabled and the battery voltage is above the minimum system voltage setting.

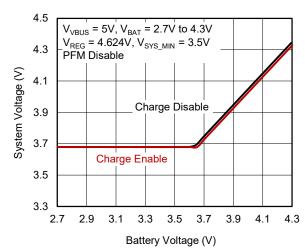


Figure 7. System Voltage vs. Battery Voltage

#### **Dynamic Power Management (DPM)**

The SGM41518 has a dynamic power management (DPM) feature. To implement DPM, the device always monitors the input current and voltage to regulate power demand from the source and avoid input adapter overloading or to meet the maximum current limits specified in the USB specs. Overloading an input source may results in either current trying to exceed the input current limit ( $I_{\text{INDPM}}$ ) or the voltage tending to fall below the input voltage limit ( $V_{\text{INDPM}}$ ). With DPM, the device keeps the VSYS regulated to its minimum setting by reducing the battery charge current adequately such that the input parameter (voltage or current) does not exceed the limit. In other words, charge current is reduced to satisfy  $I_{\text{INDPM}}$  or  $V_{\text{IN}} \geq V_{\text{INDPM}}$  whichever occurs first. DPM can be either an  $I_{\text{IN}}$  type (IINDPM) or  $V_{\text{IN}}$  type (VINDPM) depending on which limit is reached.

Changing to the supplement mode may be required if the charge current is decreased and reached to zero, but the input is still overloaded. In this case, the charger reduces the system voltage below the battery voltage to allow operation in the supplement mode and provide a portion of system power demand from the battery through the BATFET.

The IINDPM\_STAT or VINDPM\_STAT status bits are set during an IINDPM or VINDPM respectively.

#### **Battery Supplement Mode**

If the system voltage drops below the battery voltage, the BATFET gradually starts to turn on. The threshold margin is 180mV if  $V_{\text{SYS\_MIN}}$  setting is less than  $V_{\text{BAT}}$  and 45mV if  $V_{\text{SYS\_MIN}}$  setting is larger than  $V_{\text{BAT}}$ . At low discharge currents, the BATFET gate voltage is regulated ( $R_{\text{DS}}$  modulation) such that the BATFET  $V_{\text{DS}}$  stays at 25mV. At higher currents, the BATFET will turn fully on (reaching its lowest  $R_{\text{DSON}}$ ). From this point, increasing the discharge current will linearly increase the BATFET  $V_{\text{DS}}$  (determined by  $R_{\text{DSON}} \times I_{\text{D}}$ ). Use of the MOSFET linear mode at lower currents prevents swinging oscillation of entering and exiting the supplement mode.

BATFET gate regulation V-I characteristics is shown in Figure 8. If the battery voltage falls below its minimum depletion, the BATFET turns off and exits supplement mode.

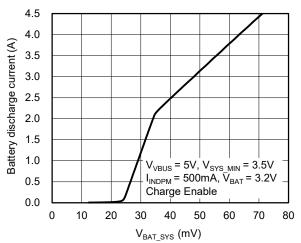


Figure 8. BATFET Gate Regulation V-I Curve

### **BATFET Control for System Power Reset** and Ship Mode

#### **Ship Mode (BATFET Disable)**

Ship mode is usually used when the system is stored or in idle state for a long time or is in shipping. In such conditions, it is better to completely disconnect battery and make system voltage zero to minimize the leakage and extend the battery life. To enter ship mode, the BATFET has to be forced off by setting BATFET\_DIS bit. The BATFET turns off immediately if BATFET\_DLY bit is 0, or turns off after a t<sub>SM\_DLY</sub> delay (12.5 seconds) if BATFET\_DLY is set.

#### Exit Ship Mode (BATFET Enable)

To exit the ship mode and enable the BATFET, one of the following can be applied:

With no input power (no operating VBUS):

- 1. Connect the adapter to the input with a valid voltage to the VBUS input.
- 2. Pull nQON pin from logic high to low to enable BATFET, for example, by shorting nQON to GND. The negative pulse width should be at least a  $t_{\text{SHIPMODE}}$  (1s TYP) for deglitching.

With the chip already powered by VBUS:

- 3. Clear BATFET\_DIS bit using host and I<sup>2</sup>C.
- 4. Set REG\_RST bit to reset all registers including BATFET\_DIS bit to default (0).
- 5. Apply a negative pulse to nQON pin (same as 2).

#### Full System Reset with BATFET Using nQON

When the input source is not present, the BATFET can act as a load on/off switch between the system and battery. This feature can be used to apply a power-on reset to the system. Host can toggle BATFET\_DIS bit to cycle power off/on and reset the system. A push-button connected to nQON pin or a negative pulse can also be used to manually force a system power cycle when BATFET is ON (BATFET\_DIS bit = 0). For this function, a negative logic pulse with a minimum width of  $t_{QON\_RST}$  (10s TYP) must be applied to the nQON pin that results in a temporary BATFET turn off for  $t_{BATFET\_RST}$  (320ms TYP) that automatically turns on afterward. This functionality can be disabled by setting BATFET\_RST\_EN bit to 0.

In summary, the nQON pin controls BATFET and system reset in two different ways:

- 1. Enable BATFET: Applying an nQON logic high to low transition with longer than  $t_{\text{SHIPMODE}}$  deglitch time (negative pulse) turns on BATFET to exit ship mode (Figure 9 left). HIZ is also enabled (EN\_HIZ = 1) when exiting shipping mode. After exiting shipping mode, the host can disable HIZ (EN\_HIZ = 0). OTG cannot be enabled (BST\_CONFIG = 1) until HIZ is disabled.
- 2. Reset BATFET: By applying a logic low for a duration of at least  $t_{QON\_RST}$  to nQON pin while VBUS is not powered and BATFET is allowed to turn on (BATFET\_DIS bit = 0), the BATFET turns off for  $t_{BATFET\_RST}$  and then it is re-enabled resulting in a system power-on reset. This function can be disabled by clearing BATFET\_RST\_EN bit (Figure 9 right).

A typical push button circuit for nQON is given in Figure 10.

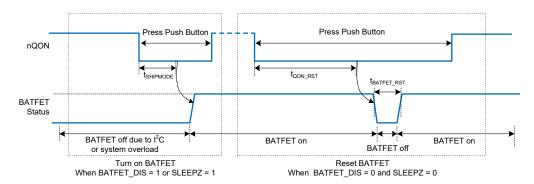


Figure 9. nQON Enable and Reset BATFET Timing

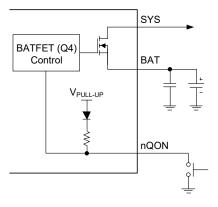


Figure 10. nQON Manual Operation Circuit

### Status Outputs Pins (STAT, nINT and PMID\_GD)

#### Power Good Indication (PG STAT Bit)

When a good input source is connected to VBUS and input type is detected, the PG\_STAT status bit goes high. A good input source is detected if all following conditions on  $V_{VBUS}$  are satisfied and input type detection is completed:

- $V_{VBUS}$  is in the operating range:  $V_{VAC\ UVLOZ} < V_{VBUS} < V_{VAC\ OV}$ .
- Device is not in sleep mode: V<sub>VBUS</sub> > V<sub>BAT</sub> + V<sub>SLEEP</sub>.
- Input source is not poor:  $V_{VBUS} > V_{VBUSMIN}$  (3.8V TYP) when  $I_{BAD\_SRC}$  (30mA TYP) loading is applied. (Poor source detection.)
- · Completed input source type detection.

#### **Charge Status (STAT Pin)**

Charging state is indicated with the open-drain STAT pin as explained in Table 4. This pin is able to drive an LED (see Figure 1). The functionality of the STAT pin is disabled if the EN ICHG MON[1:0] bits are set to 10 or 11.

**Table 4. STAT Pin Function** 

Charging State	STAT Indicator
Charging battery (or recharge)	Low (LED ON)
Charging completed	High (LED OFF)
Charging is disabled or in sleep mode	High (LED OFF)
Charge is suspended due to input over-voltage, TS fault, timer faults or system over-voltage or Boost mode is suspended (TS fault)	1Hz Blinking
EN_ICHG_MON[1:0] = 01, controlled by register only, no matter with charging state	STAT_SET[1:0]

#### nINT Interrupt Output Pin

When a new update occurs in the charger states, a  $256\mu s$  negative pulse is sent through the nINT pin to interrupt the host. The host may not continuously monitor the charger device and by receiving the interrupt, it can react and check the charger situation on time.

The following events can generate an interrupt pulse:

- 1. Faults reflected in REG0x09 register (watchdog, Boost overload, charge faults and battery over-voltage).
- 2. Charging completed.
- 3. PSEL detection identified a connected source (USB or adapter).
- 4. Input source voltage entered the "input good" range:
  - a) V<sub>VBUS</sub> exceeded V<sub>BAT</sub> (not in sleep mode).
  - b)  $V_{VBUS}$  came below  $V_{VAC\_OV}$ .
  - c)  $V_{VBUS}$  remained above  $V_{VBUSMIN}$  (3.8V TYP) when  $I_{BAD\_SRC}$  (30mA TYP) load current is applied.
- 5. Input removed or out of the "input good" range.

A DPM event (VINDPM or IINDPM) occurred (a maskable interrupt).

Once a fault happens, the INT pulse is asserted immediately and the fault bits are updated in REG0x09. Fault status is not reset in the register until the host reads it. A new fault will not assert a new INT pulse until the host reads REG0x09 and all the previous faults are cleared. Therefore, in order to read the current time faults, the host must read REG0x09 two times consecutively. The first read returns the history of the fault register status (from the time of the last read or reset) and the second one checks the current active faults. As an exception, the NTC\_FAULT bit reports the actual real-time status of TS pin.

#### PMID Voltage Indicator (PMID\_GD)

In the SGM41518, accessory devices can be connected to the charger PMID pin to draw power from the adapter through Q1 direct path or battery Boost mode. An optional external P-MOSFET can be placed between the charger PMID pin and the accessory input to disconnect the power path during over-current and over-voltage conditions. PMID\_GD is used to drive the external P-MOSFET through an inverter. PMID\_GD output high turns on the inverter, which pulls the P-MOSFET gate low to turn on the P-MOSFET, while PMID GD output low turns off the P-MOSFET.

With the adapter plugged in, when  $V_{VBUS}$  is above battery but below  $V_{ACOV}$  and passes poor source detection, PMID\_GD goes from low to high. If the Q1 current exceeds 106% of the IINDPM threshold or the adapter voltage rises above 6V  $(V_{BST\ OVP})$ , PMID\_GD will go from high to low.

If all conditions are valid, the high voltage adapter over  $V_{\text{BST\_OVP}}$  will continue to charge the battery. The external P-MOSFET will remain off to protect the accessory from over-voltage fault.

When the adapter is plug out, PMID\_GD goes low before battery Boost mode initiates.

In battery Boost mode, the device regulates the PMID voltage between 4.85V and 5.3V as a regulated power supply for accessory devices. PMID\_GD goes from low to high when the PMID voltage rises above 3.8V ( $V_{VBUSMIN}$ ). Similar to the adapter's current situation, the PMID valid voltage range is between  $V_{VBUSMIN}$  and  $V_{BST\_OVP}$ . Once the PMID voltage is outside this range, PMID\_GD will go low to disconnect the accessory device from the PMID. During Boost mode, PMID\_GD is driven high to low for all conditions exiting Boost mode such as Boost mode disable in register, ACOV, TS fault, battery drain ( $V_{BAT\_DPL}$ ), BATFET over-current ( $I_{BATFET\_OCP}$ ), etc.

#### **SGM41518 Protection Features**

#### **Monitoring of Voltage and Current**

During the converter operation, the input and system voltages (VBUS and VSYS) and switch currents are constantly monitored to assure safe operation of the device in both Buck and Boost modes, as will be explained below.

#### **Buck Mode Voltage and Current Monitoring**

#### 1. Input Over-Voltage (ACOV)

Converter switching will stop as soon as VBUS voltage exceeds  $V_{VAC\_OV}$  over-voltage limit that is programmable by OVP[1:0] in REG0x06. It is selectable between 5.5V, 6.5V, 10.5V and 14V (default) for USB or 5V, 9V or 12V adaptors respectively.

Each time VBUS exceeds the OVP limit, an INT pulse is asserted. As long as the over-voltage persists, the CHRG\_FAULT[1:0] bits are set to 01 in REG0x09. Fault will be cleared to 00 if the voltage comes back below limit (and a hysteresis threshold) and host reads the fault register. Charger resumes its normal operation when the voltage comes back below OVP limit.

#### 2. System Over-Voltage (SYSOVP)

During a system load transient, the device clamps the system voltage to protect the system components from over-voltage. The SYSOVP over-voltage limit threshold is  $350\text{mV} + \text{V}_{\text{BAT}}$ , or  $350\text{mV} + \text{V}_{\text{SYS\_MIN}}$  when in SYSMIN condition (programmed minimum system regulation voltage + 350mV). Once a SYSOVP occurs, switching stops to clamp any overshoot and a 30mA sink current is applied to SYS to pull the voltage down.

#### **Boost Mode Voltage and Current Monitoring**

#### 1. Output Short Protection for PMID

The SGM41518 real-time monitors the battery discharge current through the BATFET (Q4) to ensure safe operation in Boost mode. Under an over-current condition where the Boost input current exceeds IBATFET\_OCP, the device is latched within 100µs. When an over-current condition is detected, the BOOST\_FAULT bit of fault register is set to 1, indicating a fault in Boost operation, and an INT is asserted to notify the host.

#### 2. Output Over-Voltage Protection for PMID

In Boost mode, converter stops switching and PMID\_GD is pulled low if PMID voltage rises above regulation and exceeds the  $V_{BST\ OVP}$  over-voltage limit (6V TYP).

#### Thermal Regulation and Shutdown

#### **Buck Mode Thermal Protections**

Internal junction temperature  $(T_J)$  is always monitored to avoid overheating. A limit of +120  $^{\circ}\text{C}$  is considered for

maximum IC surface temperature in Buck mode and if  $T_J$  intends to exceed this level, the device reduces the charge current to keep maximum temperature limited to +120 °C (thermal regulation mode) and sets the THERM\_STAT bit to 1. As expected, the actual charging current is usually lower than programmed value during thermal regulation. Therefore, the safety timer runs at half clock rate and charge termination is disabled during thermal regulation.

If the junction temperature exceeds  $T_{SHUT}$  (+150°C), thermal shutdown protection arises in which the converter is turned off, CHRG\_FAULT[1:0] bits are set to 10 in the fault register and an INT pulse is sent.

When the device recovers and  $T_J$  falls below the hysteresis band of  $T_{SHUT\_HYS}$  (30°C under  $T_{SHUT}$ ), the converter resumes automatically.

#### **Boost Mode Thermal Protections**

Similar to Buck mode,  $T_J$  is monitored in Boost mode for thermal shutdown protection. If junction temperature exceeds  $T_{SHUT}$  (+150°C), the Boost mode will be disabled (BST\_CONFIG bit clears). If  $T_J$  falls below the hysteresis band of  $T_{SHUT\_HYS}$  (30°C under  $T_{SHUT}$ ), Boost can recover again by re-enabling BST\_CONFIG bit by host.

#### **Battery Protections**

#### Battery Over-Voltage Protection (BATOVP)

The over-voltage limit for the battery is 4% above the battery regulation voltage setting. In case of a BATOVP, charging or external direct charging stops right away, the BAT\_FAULT bit is set to 1 and an INT pulse is sent.

#### **Battery Over-Discharge Protection**

If battery discharges too much and  $V_{BAT}$  falls below the depletion level ( $V_{BAT\_DPL\_FALL}$ ), the device turns off BATFET to protect battery. This protection is latched and is not recovered until an input source is connected to the VBUS pin. In such condition, the battery will start charging with the small  $I_{SHORT}$  current (30mA TYP) first as long as  $V_{BAT} < V_{SHORTZ}$ . When battery voltage is increased and  $V_{SHORTZ} < V_{BAT} < V_{BATLOW}$ , the charge current will increase to the pre-charge current level programmed in the IPRECHG[3:0] register.

#### **Battery Over-Current Protection for System**

The BATFET will latch off, if its current limit is exceeded due to a short or large overload on the system ( $I_{BAT} > I_{BATFET\_OCP}$ ). To reset this latch off and enable BATFET, the "Exit Ship Mode" procedure must be followed.



#### I<sup>2</sup>C Serial Interface and Data Communication

Standard I<sup>2</sup>C interface is used to program SGM41518 parameters and get status reports. I<sup>2</sup>C is well known 2 wire serial communication interface that can connect one (or more) master device(s) to some slave devices for two-way communication. The bus lines are named serial data (SDA) and serial clock (SCL). The device that initiates a data transfer is a master. A master generates the SCL signal. Slave devices have unique addresses to identify. A master is typically a micro controller or a digital signal processor.

The SGM41518 operates as a slave device that address is 0x3B (3BH). It has sixteen 8-bit registers, numbered from REG0x00 to REG0x0F. A register read beyond REG0x0F (0x0F) returns 0xFF.

#### **Physical Layer**

The standard I<sup>2</sup>C interface of SGM41518 supports standard mode and fast mode communication speeds. The frequency of standard mode is up to 100kbits/s, while the fast mode is up to 400kbits/s. Bus lines are pulled high by weak current source or pull-up resistors and in logic high state with no clocking when the bus is free. The SDA and SCL pins are open-drain.

#### I<sup>2</sup>C Data Communication

#### **START and STOP Conditions**

A transaction is started by taking control of the bus by master if the bus is free. The transaction is terminated by releasing the bus when the data transfer job is done as shown in Figure 11. All transactions begin by the master who applies a START condition on the bus lines to take over the bus and exchange data. At the end, the master terminates the transaction by applying one (or more) STOP condition. START condition is when SCL is high and a high to low transition on the SDA is generated by master. Similarly, a STOP is defined when SCL is high and SDA goes from low to high. START and STOP are always generated by a master. After a START and before a STOP the bus is considered busy.

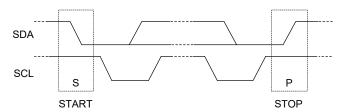


Figure 11. I<sup>2</sup>C Bus in START and STOP Conditions

#### **Data Bit Transmission and Validity**

The data bit (high or low) must remain stable on the SDA line during the HIGH period of the clock. The state of the SDA can only change when the clock (SCL) is LOW. For each data bit transmission, one clock pulse is generated by master. Bit transfer in I<sup>2</sup>C is shown in Figure 12.

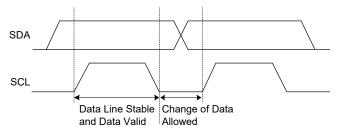


Figure 12. I<sup>2</sup>C Bus Bit Transfer

#### **Byte Format**

Data is transmitted in 8-bit packets (one byte at a time). The number of bytes in one transaction is not limited. In each packet, the 8 bits are sent successively with the Most Significant Bit (MSB) first. An acknowledge (or not-acknowledge) bit must come after the 8 data bits. This bit informs the transmitter whether the receiver is ready to proceed for the next byte or not. Figure 13 shows the byte transfer process with I<sup>2</sup>C interface.

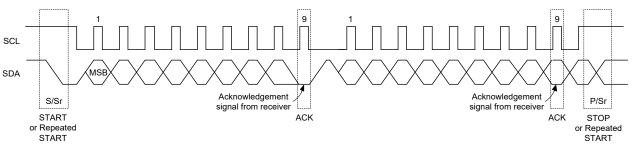


Figure 13. Byte Transfer Process



#### Acknowledge (ACK) and Not Acknowledge (NCK)

After transmission of each byte by transmitter, an acknowledge bit is replied by the receiver as ninth bit. With the acknowledge bit, the receiver informs the transmitter that the byte was received, and another byte is expected or can be sent (ACK) or it is not expected (NCK = not ACK). Clock (SCL) is always generated by the master, including for the acknowledge clock pulse. SDA line is released for receiver control during the acknowledge clock pulse, and the receiver can pull the SDA line low as ACK (reply a 0 bit) or let it be high as NCK during the SCL high pulse. After that, the master can either STOP (P) to end the transaction or send a new START (S) condition to start a new transfer (called repeated start). For example, when master wants to read a register in slave, one start is needed to send the slave address and register address, and then, without a stop condition, another start is sent by master to initiate the receiving transaction from slave. Master then sends the STOP condition and releases the bus.

#### **Data Direction Bit and Addressing Slaves**

The first byte sent by master after the START is always the target slave address (7 bits) and an eighth data-direction bit (R/W). R/W bit is 0 for a WRITE transaction and 1 for READ

(when master is asking for data). Data direction is the same for all next bytes of the transaction. To reverse it, a new START or repeated START condition must be sent by master (STOP will end the transaction). Usually the second byte is a WRITE sending the register address that is supposed to be accesses in the next byte(s). The data transfer transaction is shown in Figure 14.

**WRITE:** If the master wants to write in the register, the third byte can be written directly as shown in Figure 15 for a single write data transfer. After receiving the ACK, master may issue a STOP condition to end the transaction or send the next register data, which will be written to the next address in a slave as multi-write. A STOP is needed after sending the last data.

**READ:** If the master wants to read a single register (Figure 16), it sends a new START condition along with device address with R/W bit = 1. After ACK is received, master reads the SDA line to receive the content of the register. Master replies with NCK to inform slave that no more data is needed (single read) or it can send an ACK to request for sending the next register content (multi-read). This can continue until a NCK is sent by master. A STOP must be sent by master in any case to end the transaction.

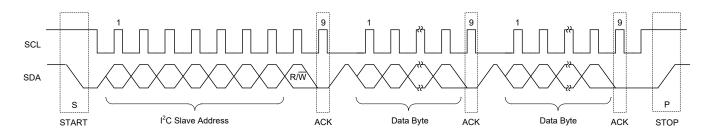


Figure 14. Data Transfer Transaction

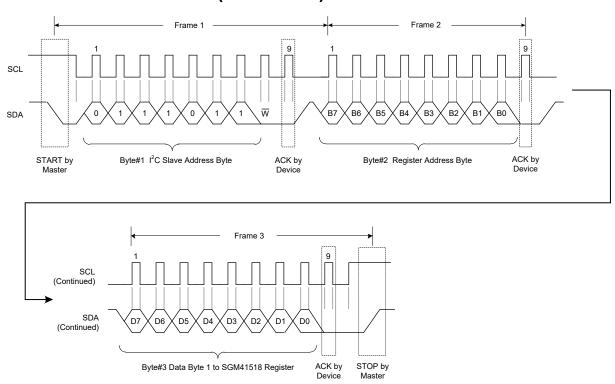


Figure 15. A Single Write Transaction

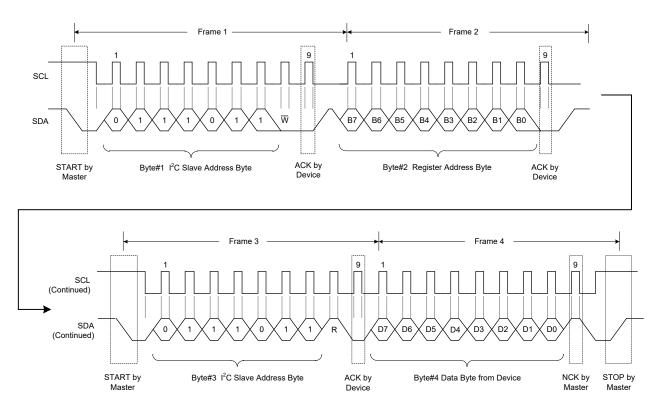


Figure 16. A Single Read Transaction

Data Transactions with Multi-Read or Multi-Write Multi-read and multi-write are supported by SGM41518 for REG0x00 through REG0x0F registers, as explained in Figure 17 and Figure 18. In the multi-write, every new data byte sent by master is written to the next register of the device. A STOP is sent whenever master is done with writing into device registers.

In a multi-read transaction, after receiving the first register data (its address is already written to the slave), the master replies with an ACK to ask the slave for sending the next register data. This can continue as much as it is needed by master. Master sends back an NCK after the last received byte and issues a STOP condition.

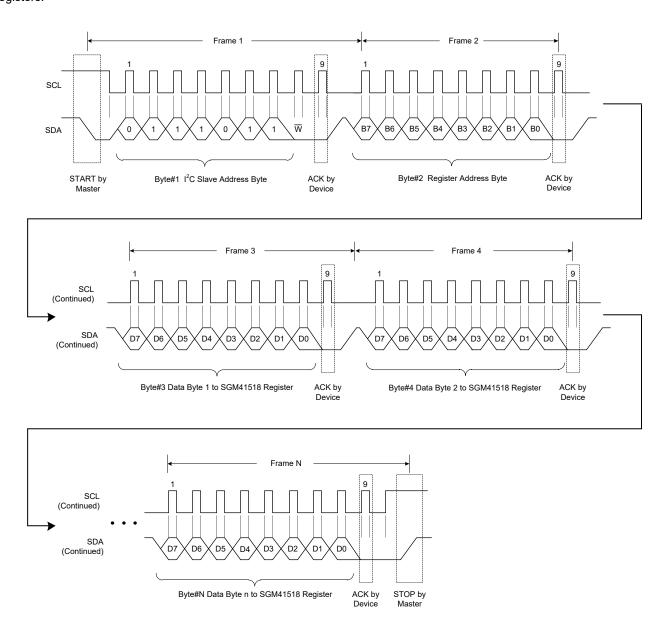


Figure 17. A Multi-Write Transaction

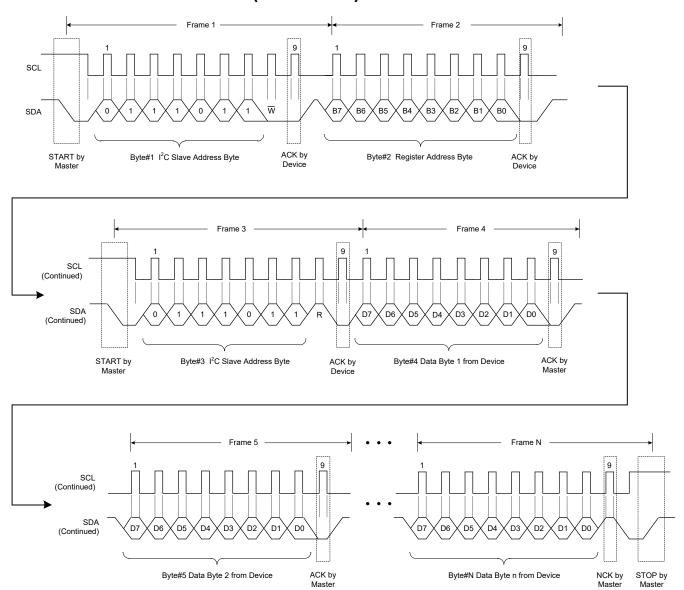


Figure 18. A Multi-Read Transaction

#### **REGISTER MAPS**

All registers are 8-bit and individual bits are named from D[0] (LSB) to D[7] (MSB).

#### I<sup>2</sup>C Register Address Map

FUNCTION	STAT	FLAG	MASK	THRESHOLD SETTING	ENABLE
CHARGE	0x08[4:3]	0x09[5:4]	_	_	0x01[4]
VREG	_	_	_	0x04[7:3]	_
VREG_FT	_	_	_	0x0F[7:6]	0x0F[7:6]
ICHG	_	-	_	0x02[5:0]	_
IPRECHG	_	_	_	0x03[7:4]	_
ITERM	_	_	_	0x03[3:0]	0x05[7]
VRECHG	_	_	_	0x04[0]	_
CHG_TIMER	_	0x09[5:4]	_	0x05[2]	0x05[3]
TOPOFF_TIMER	0x0A[3]	_	_	0x04[2:1]	0x04[2:1]
TMR2X	_	-	-	-	0x07[6]
VINDPM	0x0A[6]	_	0x0A[1]	0x06[3:0] 0x0F[1:0]	_
VDPM_BAT_TRACK	_	_	_	0x07[1:0]	0x07[1:0]
IINDPM	0x0A[5]	_	0x0A[0]	0x00[4:0]	_
Q1_FULLON	_	_	_	0x02[6]	_
VBUS	0x08[7:5] 0x0A[7]	_	_	_	-
PG	0x08[2]	_	_	_	_
IINDET	_	_	_	-	0x07[7]
EN_ICHG_MON	_	_	_	0x00[6:5]	0x00[6:5]
STAT	_	_	_	0x0F[3:2]	0x00[6:5]
SYS_MIN	0x08[0]	_	_	0x01[3:1]	-
HIZ MODE	_	_	_	-	0x00[7]
WATCHDOG	_	0x09[7]	_	0x05[5:4]	0x05[5:4]
WD_RST	_	_	_	-	0x01[6]
OTG	0x08[7:5]	-	_	0x06[5:4]	0x01[5]
MIN_BAT_SEL	_	_	_	0x01[0]	-
BATFET	-	-	_	0x07[3]	0x07[5]
BATFET_RST	_	_	_	-	0x07[2]
PFM	_	_	_	-	0x01[7]
JEITA	_	_	_	-	0x0D[0]
JEITA_VT2	_	_	_	0x0C[3:2]	-
JEITA_VT3	_	_	_	0x0C[1:0]	_
JEITA_VSET_L	_	-	-	0x0C[7]	-
JEITA_VSET_H	-	_	_	0x07[4]	_
JEITA_ISET_L	_	_	_	0x05[0]	0x0C[6]
JEITA_ISET_H	-	-	_	0x0C[5:4]	-
TS_STAT	0x09[2:0]	-	-	-	-
TREG	0x08[1]	_	_	0x05[1]	_
TSHUT	-	0x09[5:4]	-	-	-
BUS OVP	0x0A[2]	0x09[5:4]	_	0x06[7:6]	_
BAT OVP	_	0x09[3]	_	_	_
BOOST FAULT	-	0x09[6]	_	-	_
REG_RST	_	_	_	-	0x0B[7]

#### SGM41518

### **REGISTER MAPS (continued)**

I<sup>2</sup>C Slave Address of SGM41518: 0x3B

Bit Types:

R: Read only R/W: Read/Write

n: Parameter code formed by the bits as an unsigned binary number.

#### **REG0x00:** Input Current Limit Register [Reset = 0x17]

BITS	BIT NAME	DEFAULT	TYPE		DESCRIPTION	RESET BY
D[7]	EN_HIZ	0	R/W		It) /BUS pin is effectively disconnected from internal age current may exist.	REG_RST or Watchdog
D[6:5]	EN_ICHG_MON[1:0]	00	R/W	Enable STAT Pin Function  00 = Enable following charging state (default)  01 = Enable following STAT_SET[1:0] bits  10 = Disable (float pin)  11 = Disable (float pin)  These bits turn on or off the function of the STAT open-drain output pin (charge status or customer customized indicator).		REG_RST
				1 = 1600mA IINDPM[3] 1 = 800mA	Input Current Limit Value (n: 5 bits): = 100 + 100n (mA) Offset: 100mA	
D[4:0]	IINDPM[4:0]	10111	R/W		Range: 100mA (00000) - 3.2A (11111) Default: 2400mA (10111), not typical	REG_RST
				IINDPM[1] 1 = 200mA	IINDPM changes after an input source detection.	
					Host can overwrite IINDPM after input source detection is completed.	

### REG0x01: Charger Control 1 Register [Reset = 0x1A]

BITS	BIT NAME	DEFAULT	TYPE	DESCRIPTION	RESET BY
D[7]	PFM_DIS	0	R/W	Enable PFM Mode 0 = Enable (default) 1 = Disable Enable Pulse Frequency Modulation. PFM is normally used to save power at light load by reducing converter switching frequency.	REG_RST
D[6]	WD_RST	0	R/W	I <sup>2</sup> C Watchdog Timer Reset 0 = Normal (default) 1 = Reset Watchdog Timer Reset Control Bit. Write 1 to this bit to avoid watchdog expiry. WD_RST resets to 0 after watchdog timer reset (expiry).	REG_RST or Watchdog
D[5]	BST_CONFIG	0	R/W	Enable OTG 0 = OTG disable (default) 1 = OTG enable This bit has priority over charge enable in the CHG_CONFIG.	REG_RST or Watchdog
D[4]	CHG_CONFIG	1	R/W	Enable Battery Charging 0 = Charge disable 1 = Charge enable (default) Charge is enabled when CHG_CONFIG bit is 1 and nCE pin is pulled low.	REG_RST or Watchdog
D[3:1]	SYS_MIN[2:0]	101	R/W	Minimum System Voltage 000 = 2.6V 001 = 2.8V 010 = 3V 011 = 3.2V 100 = 3.4V 101 = 3.5V (default) 110 = 3.6V 111 = 3.7V Minimum System Voltage Value. Offset: 2.6V Range: 2.6V (000) - 3.7V (111) Default: 3.5V (101)	REG_RST
D[0]	MIN_BAT_SEL	0	R/W	Minimum Battery Voltage for Boost Mode  0 = 3V V <sub>BAT</sub> falling (default)  1 = 2.6V V <sub>BAT</sub> falling  Default:  V <sub>BAT</sub> falling, V <sub>BATLOW_BST</sub> = 3V.  V <sub>BAT</sub> rising, V <sub>BATLOW_BST</sub> = 3.2V.	REG_RST

#### **REG0x02: Charge Current Limit Register [Reset = 0x91]**

BITS	BIT NAME	DEFAULT	TYPE		DESCRIPTION	RESET BY
D[7]	Reserved	1	R/W	Reserved		REG_RST or Watchdog
D[6]	Q1_FULLON	0	R/W	VBUS FET Switch (Q1) 0 = Use higher R <sub>DSON</sub> if I <sub>INDPM</sub> < 700mA (for better accuracy) (default) 1 = Use lower R <sub>DSON</sub> always (fully ON for better efficiency) Used to control the on-resistance of Q1 (VBUS switch) for better input current measurement accuracy. Note that Q1 is off in Boost mode.		REG_RST
				ICHG[5] 1 = 640mA		
		040004	DAM	ICHG[4] 1 = 320mA	Fast Charge Current Value (n: 6 bits): = 20n (mA) (n ≤ 63) Offset: 0mA	REG RST
D[5:0]	ICHG[5:0]			ICHG[3] 1 = 160mA		
D[3.0]	iono[5.0]	010001	R/W	ICHG[2] 1 = 80mA	Range: 0mA (000000) - 1260mA (111111), Default: 340mA (010001)	or Watchdog
				ICHG[1] 1 = 40mA	Note: Setting I <sub>CHG</sub> = 0mA disables charge.	
				ICHG[0] 1 = 20mA		

#### **REG0x03: Pre-Charge and Termination Current Limit Register [Reset = 0x12]**

BITS	BIT NAME	DEFAULT	TYPE		DESCRIPTION	
		0	R/W	IPRECHG[3] 1 = 160mA	Pre-Charge Current Limit (n: 4 bits): = 20 + 20n (mA) (n ≤ 12)	
D[7:4]	D[7:4] IPRECHG[3:0]	0	R/W	IPRECHG[2] 1 = 80mA	Offset: 20mA Range: 20mA (0000) - 260mA (1100)	REG_RST
D[1.4]		0	R/W	IPRECHG[1] 1 = 40mA	Default: 40mA (0001)  Note:	or Watchdog
		1		IPRECHG[0] 1 = 20mA	Values above 12D = 1100 (260mA) are clamped to 12D = 1100 (260mA).	
		0	R/W	ITERM[3] 1 = 160mA	Termination Current Limit (n: 4 bits): = 20 + 20n (mA)  Offset: 20mA Range: 20mA (0000) - 320mA (1111)	REG_RST or Watchdog
D[3:0]	ITERM[3:0]	0	R/W	ITERM[2] 1 = 80mA		
D[3:0]	11 LIXW[3.0]	1	R/W	ITERM[1] 1 = 40mA		
		0	R/W	ITERM[0] 1 = 20mA	Default: 60mA (0010)	

### **REG0x04:** Battery Voltage Limit Register [Reset = 0x58]

BITS	BIT NAME	DEFAULT	TYPE		DESCRIPTION	RESET BY
		0	R/W	VREG[4] 1 = 512mV	Charge Voltage Limit (n: 5 bits): = 3856 + 32n (mV) if n ≤ 24, n ≠ 15;	
		1	R/W	VREG[3] 1 = 256mV	= 4.352V if n = 15 Offset: 3.856V	
D[7:3]	VREG[4:0]	0	R/W	VREG[2] 1 = 128mV	Range: 3.856V (00000) - 4.624V (11000) Default: 4.208V (01011) Special Value: 4.352V (01111)	REG_RST or Watchdog
		1 R/	R/W	VREG[1] 1 = 64mV	Note:	
		1	R/W	VREG[0] 1 = 32mV	Values above 24D = 11000 (4.624V) are clamped to 24D = 11000 (4.624V).	
D[2:1]	TOPOFF_TIMER[1:0]	00	R/W	Top-Off Timer  00 = Disabled (default)  01 = 15 minutes  10 = 30 minutes  11 = 45 minutes  The charge extension time added after the termination condition is detected.  If disabled, charging terminates as soon as termination conditions are met.		REG_RST or Watchdog
D[0]	VRECHG	0	R/W	Battery Recharge Threshold 0 = 100mV below VREG[4:0] (default) 1 = 200mV below VREG[4:0] A recharge cycle will start if a fully charged battery voltage drops below VREG - VRECHG settings.		REG_RST or Watchdog

#### **REG0x05: Charger Control 2 Register [Reset = 0x9F]**

BITS	BIT NAME	DEFAULT	TYPE	DESCRIPTION	RESET BY
D[7]	EN_TERM	1	R/W	Charging Termination Enable 0 = Disable 1 = Enable (default)	REG_RST or Watchdog
D[6]	Reserved	0	R/W	Reserved	REG_RST or Watchdog
D[5:4]	WATCHDOG[1:0]	01	R/W	Watchdog Timer Setting 00 = Disable watchdog timer 01 = 40s (default) 10 = 80s 11 = 160s Expiry time of the watchdog timer if it is not reset.	REG_RST or Watchdog
D[3]	EN_TIMER	1	R/W	Charge Safety Timer Enable 0 = Disable 1 = Enable (default) When enabled the pre-charge and fast charge periods are included in the timing.	REG_RST or Watchdog
D[2]	CHG_TIMER	1	R/W	Charge Safety Timer Setting 0 = 20h 1 = 11.5h (default)	REG_RST or Watchdog
D[1]	TREG	1	R/W	Thermal Regulation Threshold  0 = 80°C  1 = 120°C (default)  For Buck mode.	REG_RST or Watchdog
D[0]	JEITA_ISET_L (0°C - 10°C)	1	R/W	JEITA Charging Current $0 = 50\%$ of $I_{CHG}$ $1 = 20\%$ of $I_{CHG}$ (default) When JEITA_ISET_L_EN = 1.	REG_RST or Watchdog

#### **REG0x06: Charger Control 3 Register [Reset = 0xD6]**

BITS	BIT NAME	DEFAULT	TYPE		DESCRIPTION	RESET BY
D[7:6]	OVP[1:0]	11	R/W	VAC Pin OVP Threshold  00 = 5.5V  01 = 6.5V (5V input)  10 = 10.5V (9V input)  11 = 14V (12V input) (default)  OVP Threshold for Input Supply.		REG_RST
D[5:4]	BOOSTV[1:0]	01	R/W	Boost Mode Voltage Regulation 00 = 4.85V 01 = 5V (default) 10 = 5.15V 11 = 5.30V		REG_RST
				VINDPM[3] 1 = 800mV	VINDPM Threshold (n: 4 bits): = Offset + 0.1n (V) Offset: 3.9V (VINDPM OS = 00, default)	
				VINDPM[2] 1 = 400mV	Range: 3.9V (0000) - 5.4V (1111) Default: 4.5V (0110)	
D[3:0]	VINDPM[3:0]	0110	R/W	VINDPM[1]	Offset: 5.9V (VINDPM_OS = 01) Range: 5.9V (0000) - 7.4V (1111)	REG_RST
				1 =200mV	Offset: 7.5V (VINDPM_OS = 10) Range: 7.5V (0000) - 9V (1111)	
				VINDPM[0] 1 =100mV	Offset: 10.5V (VINDPM_OS = 11) Range: 10.5V (0000) - 12V (1111)	

#### **REG0x07: Charger Control 4 Register [Reset = 0x4C]**

BITS	BIT NAME	DEFAULT	TYPE	DESCRIPTION	RESET BY
D[7]	IINDET_EN	0	R/W	Input Current Limit Detection 0 = Not in input current limit detection (default) 1 = Force input current limit detection when VBUS is present Reloads with 0 when input detection is completed.	REG_RST or Watchdog
D[6]	TMR2X_EN	1	R/W	Enable Half Clock Rate Safety Timer 0 = Disable 1 = Safety timer slow down during DPM, JEITA cool, or thermal regulation (default) Slow down by a factor of 2.	REG_RST or Watchdog
D[5]	BATFET_DIS	0	R/W	Disable BATFET  0 = Allow BATFET (Q4) to turn on (default)  1 = Turn off BATFET (Q4) after a t <sub>SM_DLY</sub> delay time (REG0x07 D[3])  t <sub>SM_DLY</sub> is typically 12.5 seconds.	REG_RST
D[4]	JEITA_VSET_H (45°C - 60°C)	0	R/W	JEITA Charging Voltage 0 = Set charge voltage to the lower of 4.1V and V <sub>REG</sub> (default) 1 = Set charge voltage to V <sub>REG</sub>	REG_RST or Watchdog
D[3]	BATFET_DLY	1	R/W	BATFET Turn Off Delay Control 0 = Turn off BATFET immediately 1 = Turn off BATFET after t <sub>SM_DLY</sub> (default) BATFET_DIS bit is set.	REG_RST
D[2]	BATFET_RST_EN	1	R/W	Enable BATFET Reset 0 = Disable BATFET reset 1 = Enable BATFET reset (default)	REG_RST or Watchdog
D[1:0]	VDPM_BAT_ TRACK[1:0]	00	R/W	Dynamic VINDPM Tracking 00 = Disable (V <sub>INDPM</sub> set by register) 01 = V <sub>BAT</sub> + 200mV 10 = V <sub>BAT</sub> + 250mV 11 = V <sub>BAT</sub> + 300mV Set V <sub>INDPM</sub> to track V <sub>BAT</sub> voltage. Actual V <sub>INDPM</sub> is the larger of VINDPM[3:0] and this register value.	REG_RST

### REG0x08: Charger Status 1 Register [Reset = 0xXX]

BITS	BIT NAME	DEFAULT	TYPE	DESCRIPTION	RESET BY
D[7:5]	VBUS_STAT[2:0]	xxx	R	VBUS Status Register 000 = No input 001 = USB host SDP (500mA) → PSEL HIGH 011 = Adapter 2.4A → PSEL LOW 111 = OTG Other values are reserved. Current limit value is reported in IINDPM[4:0] register.	N/A
D[4:3]	CHRG_STAT[1:0]	xx	R	Charging Status  00 = Charge disable  01 = Pre-charge (V <sub>BAT</sub> < V <sub>BATLOW</sub> )  10 = Fast charging (constant current or voltage)  11 = Charging terminated	N/A
D[2]	PG_STAT	х	R	Input Power Status (VBUS in good voltage range and not poor) 0 = Input power source is not good 1 = Input power source is good	N/A
D[1]	THERM_STAT	х	R	Thermal Regulation Status 0 = Not in thermal regulation 1 = In thermal regulation	N/A
D[0]	VSYS_STAT	х	R	System Voltage Regulation Status  0 = Not in VSYSMIN regulation (V <sub>BAT</sub> > V <sub>SYS_MIN</sub> )  1 = In VSYSMIN regulation (V <sub>BAT</sub> < V <sub>SYS_MIN</sub> )	N/A

#### **REG0x09:** Fault Register [Reset = 0xXX]

BITS	BIT NAME	DEFAULT	TYPE	DESCRIPTION	RESET BY
D[7]	WATCHDOG_FAULT	х	R	Watchdog Fault Status 0 = Normal (no fault) 1 = Watchdog timer expired	N/A
D[6]	BOOST_FAULT	x	R	Boost Mode Fault Status 0 = Normal 1 = PMID overloaded in OTG or battery voltage too low (any condition that prevents Boost starting)	N/A
D[5:4]	CHRG_FAULT[1:0]	xx	R	Charging Fault Status  00 = Normal  01 = Input fault (VAC OVP or V <sub>BAT</sub> < V <sub>VBUS</sub> < 3.8V)  10 = Thermal shutdown  11 = Charge safety timer expired	N/A
D[3]	BAT_FAULT	х	R	Battery Fault Status 0 = Normal 1 = Battery over-voltage (BATOVP)	N/A
D[2:0]	NTC_FAULT[2:0]	xxx	R	JEITA Condition Based on Battery NTC Temperature Measurement 000 = Normal 010 = Warm (Buck mode only) 011 = Cool (Buck mode only) 101 = Cold 110 = Hot NTC fault bits are updated in real-time and does not need a read to reset.	N/A

### REG0x0A: Charger Status2 Register [Reset = 0xXX]

BITS	BIT NAME	DEFAULT	TYPE	DESCRIPTION	RESET BY
D[7]	VBUS_GD	х	R	Good Input Source Detected 0 = A good VBUS is not attached 1 = A good VBUS attached	N/A
D[6]	VINDPM_STAT	х	R	Input Voltage Regulation (Dynamic Power Management) 0 = Not in VINDPM 1 = In VINDPM	N/A
D[5]	IINDPM_STAT	х	R	Input Current Regulation (Dynamic Power Management) 0 = Not in IINDPM 1 = In IINDPM	N/A
D[4]	Reserved	х	R	Reserved	N/A
D[3]	TOPOFF_ACTIVE	х	R	Active Top-Off Timer Counting Status 0 = Top-off timer not counting 1 = Top-off timer counting	N/A
D[2]	ACOV_STAT	х	R	Input Over-Voltage Status (AC adaptor is the input source) 0 = No over-voltage (no ACOV) 1 = Over-voltage detected (ACOV)	N/A
D[1]	VINDPM_INT_MASK	0	R/W	VINDPM Event Detection Interrupt Mask 0 = Allow VINDPM INT pulse 1 = Mask VINDPM INT pulse	REG_RST
D[0]	IINDPM_INT_MASK	0	R/W	IINDPM Event Detection Mask 0 = Allow IINDPM to send INT pulse 1 = Mask IINDPM INT pulse	REG_RST

#### **REG0x0B:** Part Information Register [Reset = 0x6X]

BITS	BIT NAME	DEFAULT	TYPE	DESCRIPTION	RESET BY
D[7]	REG_RST	0	R/W	Register Reset 0 = No effect (keep current register settings) (default) 1 = Reset R/W bits of all registers to the default and reset safety timer (it also resets itself to 0 after register reset is completed.)	REG_RST
DIE-31	DNI(3·01	1	R	Part ID 1100 = SGM41518	N/A
D[6:3]	PN[3:0]	0	K		
		х			
D[2]	SGMPART	1	R		N/A
D[1:0]	DEV_REV[1:0]	XX	R	Revision	N/A

#### **REG0x0C:** Charger Control 5 Register [Reset = 0x75]

BITS	BIT NAME	DEFAULT	TYPE	DESCRIPTION	RESET BY
D[7]	JEITA_VSET_L (0°C - 10°C)	0	R/W	JEITA Charging Voltage 0 = Set charge voltage to V <sub>REG</sub> (default) 1 = Set charge voltage to the lower of 4.1V and V <sub>REG</sub>	REG_RST or Watchdog
D[6]	JEITA_ISET_L_EN (0°C - 10°C)	1	R/W	Charge Enable during Cool Temperature 0 = Disable 1 = Enable (default)	REG_RST or Watchdog
D[5:4]	JEITA_ISET_H[1:0] (45°C - 60°C)	11	R/W	Charge Current Setting during Warm Temperature $00 = 0\%$ of $I_{CHG}$ $01 = 20\%$ of $I_{CHG}$ $10 = 50\%$ of $I_{CHG}$ $11 = 100\%$ of $I_{CHG}$ (default) In warm condition, the safety timer does not become 2X.	REG_RST or Watchdog
D[3:2]	JEITA_VT2[1:0]	01	R/W	JEITA Cool Threshold Setting $00 = V_{T2} = 70.75\%$ (5.5°C) $01 = V_{T2} = 68.25\%$ (10°C) (default) $10 = V_{T2} = 65.25\%$ (15°C) $11 = V_{T2} = 62.25\%$ (20°C)	REG_RST or Watchdog
D[1:0]	JEITA_VT3[1:0]	01	R/W	JEITA Warm Threshold Setting $00 = V_{T3} = 48.25\% (40^{\circ}\text{C})$ $01 = V_{T3} = 44.75\% (45^{\circ}\text{C}) (default)$ $10 = V_{T3} = 40.75\% (50.5^{\circ}\text{C})$ $11 = V_{T3} = 37.75\% (54.5^{\circ}\text{C})$	REG_RST or Watchdog

#### **REG0x0D:** Charger Control 6 Register [Reset = 0x01]

BITS	BIT NAME	DEFAULT	TYPE	DESCRIPTION	RESET BY
D[7:1]	Reserved	0000000	R/W	I Recented	REG_RST or Watchdog
D[0]	JEITA_EN	1	R/W	JEITA Enable 0 = Disable 1 = Enable (default)	REG_RST or Watchdog

#### REG0x0E: Reserved [Reset = 0xXX]

BITS	BIT NAME	DEFAULT	TYPE	DESCRIPTION	RESET BY
D[7:0]	Reserved	xxxxxxx	R	Reserved	N/A

**REG0x0F:** Charger Control 7 Register [Reset = 0x00]

BITS	BIT NAME	DEFAULT	TYPE	DESCRIPTION	RESET BY
D[7:6]	VREG_FT	00	R/W	VREG Fine Tuning 00 = Disable (default) 01 = V <sub>REG</sub> + 8mV 10 = V <sub>REG</sub> - 8mV 11 = V <sub>REG</sub> - 16mV	REG_RST or Watchdog
D[5:4]	Reserved	00	R/W	Reserved	REG_RST or Watchdog
D[3:2]	STAT_SET[1:0]	00	R/W	STAT Pin Output Setting 00 = LED off (HIZ) (default) 01 = LED on (Low) 10 = LED blinking 1s on 1s off 11 = LED blinking 1s on 3s off This bits only takes effect when EN_ICHG_MON[1:0] = 01.	REG_RST or Watchdog
D[1:0]	VINDPM_OS[1:0]	00	R/W	VINDPM Offset 00 = 3.9V (default) 01 = 5.9V 10 = 7.5V 11 = 10.5V	REG_RST

#### **APPLICATION INFORMATION**

The SGM41518 is typically used as a charger with power path management in smart phones, tablets and other portable devices. In the design, it comes along with a host controller (a processor with I<sup>2</sup>C interface) and a single-cell Li-lon or Li-polymer battery.

#### **Detailed Design Procedure**

#### **Inductor Design**

Small energy storage elements (inductor and capacitor) can be used due to the high frequency (1.5MHz) switching converter used in the SGM41518. Inductor should tolerate currents higher than the maximum charge current ( $I_{CHG}$ ) plus half the inductor peak to peak ripple current ( $\Delta I$ ) without saturation:

$$I_{SAT} > I_{CHG} + \frac{\Delta I}{2}$$
 (3)

The inductor ripple current is determined by the input voltage ( $V_{VBUS}$ ), duty cycle (D =  $V_{BAT}/V_{VBUS}$ ), switching frequency ( $f_S$  = 1.5MHz) and the inductance (L). In CCM:

$$\Delta I = \frac{V_{VBUS} \times D \times (1 - D)}{f_{S} \times L} \tag{4}$$

Inductor ripple current is maximum when D  $\approx$  0.5. If the input voltage range (V<sub>VBUS</sub>) is limited higher, D values can be considered.

In the practical designs, inductor peak to peak current ripple is selected in a range between 20% to 40% of the maximum DC current  $\Delta I = (0.2 \sim 0.4) \times I_{CHG}$  for a good trade-off between inductor size and efficiency. Selecting higher ripple allows choosing of smaller inductance.

For each application,  $V_{VBUS}$  and  $I_{CHG}$  are known, so L can be calculated from (4) and current rating of the inductor can be selected from (3). Choose an inductor that has small DCR and core losses at 1.5MHz to have high efficiency and cool operation at full load.

#### **Input Capacitor Design**

Select low ESR ceramic input capacitor (X7R or X5R) with sufficient voltage and RMS ripple current rating for decoupling of the input switching ripple current ( $I_{CIN}$ ). The RMS ripple

current in the worst case is around the  $I_{CHG}/2$  when D  $\approx$  0.5. If the converter does not operate at D  $\approx$  50%, the worst case capacitor RMS current can be estimated from (5) in which D is the closest operating duty cycle to 0.5.

$$I_{CIN} = I_{CHG} \times \sqrt{D \times (1 - D)}$$
(5)

For SGM41518, place  $C_{\text{IN}}$  across PMID and GND pins close to the chip. Voltage rating of the capacitor must be at least 25% higher than the normal input voltage to minimize voltage derating. For a 13.5V input voltage, the preferred rating is 25V or higher.

A  $C_{IN}$  = 22 $\mu$ F is suggested.

#### **Output Capacitor Design**

The output capacitance (on the system) must have enough RMS (ripple) current rating to carry the inductor switching ripple and provide enough energy for system transient current demands.  $I_{\text{COUT}}$  ( $I_{\text{COUT}}$  RMS current) can be calculated by:

$$I_{\text{COUT}} = \frac{I_{\text{RIPPLE}}}{2 \times \sqrt{3}} \approx 0.29 \times I_{\text{RIPPLE}}$$
(6)

And the output voltage ripple can be calculated by:

$$\Delta V_{o} = \frac{V_{out}}{8LC_{out}f_{s}^{2}} \left(1 - \frac{V_{out}}{V_{VBUS}}\right)$$
 (7)

Increasing L or  $C_{\text{OUT}}$  (the LC filter) can reduce the ripple.

The internal loop compensation of the device is optimized for > 22µF ceramic output capacitor. 10V, X7R (or X5R) ceramic capacitors are recommended for the output.

#### Input Power Supply Considerations

To power the system from the SGM41518, either an input power source with a voltage between 3.9V to 13.5V and at least 100mA current rating should power VBUS, or a single-cell Li-lon battery with voltage higher than  $V_{\text{BAT\_UVLOZ}}$  should be connected to BAT pin of the device. The input source must have enough current rating to allow maximum power delivery through charger (Buck converter) to the system.

#### **APPLICATION INFORMATION (continued)**

#### **Layout Guidelines**

The switching node (SW) creates very high frequency noises, which are several times higher than f<sub>SW</sub> (1.5MHz) due to sharp rise and fall of the voltage and current in the switches. To reduce the ringing issues and noise generation, it is important to design a proper layout for minimizing the current path impedance and loop area. A graphical guideline for the current loops and their frequency content is provided in Figure 19. The following considerations can help to make a better layout.

- 1. Place the input capacitor between PMID and GND pins as close as possible to the chip with shortest copper connections (avoid vias). Choose the smallest capacitor size.
- 2. Connect one pin of the inductor as close as possible to the SW pin of the device and minimize the copper area connected to the SW node to reduce capacitive coupling from SW area to nearby signal traces. This decreases the noise through parasitic stray capacitances displacement currents to other conductors. SW connection should be wide enough to carry the charging current. Keep other signals and traces away from SW if possible.
- 3. Place output capacitor GND pin as close as possible to the GND pin of the device and the GND pin of input capacitor C<sub>IN</sub>.

It is better to avoid using vias for these connections and keep the high frequency current paths short enough and on the same layer. A GND copper layer under the component layer helps to reduce noise emissions. Pay attention to the DC current and AC current paths in the layout and keep them short and decoupled as much as possible.

- 4. For analog signals, it is better to use a separate analog ground (AGND) branched only at one point from GND pin. To avoid high current flow through the AGND path, it should be connected to GND only at one point (preferably the GND pin).
- 5. Place decoupling capacitors close to the IC pins with the shortest copper connections.
- 6. Solder the exposed thermal pad of the package to the PCB ground planes. Ensure that there are enough thermal vias directly under the IC, connecting to the ground plane on the other layers for better heat dissipation and cooling of the device.
- 7. Select proper sizes for the vias and ensure enough copper is available to carry the current for a given current path. Vias usually have some considerable parasitic inductance and resistance.

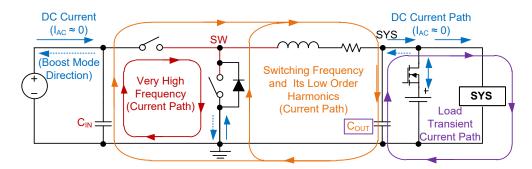


Figure 19. The Paths and Loops Carrying High Frequency, DC Currents and Very High Frequency (for Layout Design Consideration)

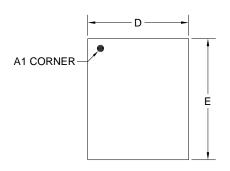
#### **REVISION HISTORY**

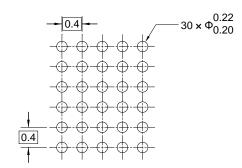
NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Original (SEPTEMBER 2022) to REV.A

Page

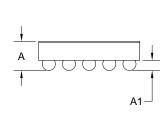
## PACKAGE OUTLINE DIMENSIONS WLCSP-2.0×2.4-30B

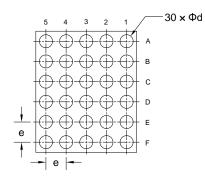




**TOP VIEW** 

RECOMMENDED LAND PATTERN (Unit: mm)





**SIDE VIEW** 

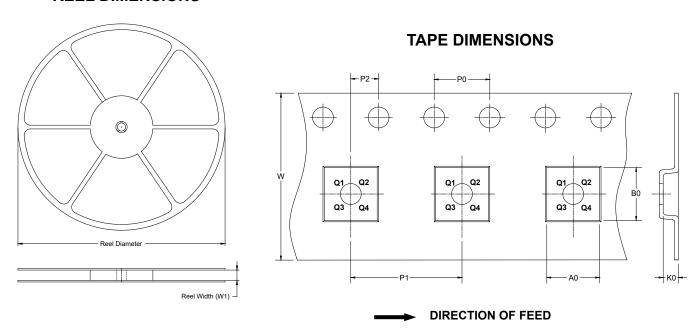
**BOTTOM VIEW** 

Symbol	Dimensions In Millimeters							
Symbol	MIN	MOD	MAX					
Α	0.525	0.575	0.625					
A1	0.180	0.200	0.220					
D	1.970	2.000	2.030					
E	2.370	2.400	2.430					
d	0.230	0.260	0.290					
е	0.400 BSC							

NOTE: This drawing is subject to change without notice.

#### TAPE AND REEL INFORMATION

#### **REEL DIMENSIONS**

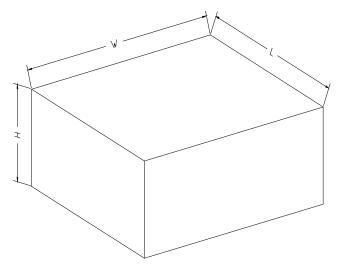


NOTE: The picture is only for reference. Please make the object as the standard.

#### **KEY PARAMETER LIST OF TAPE AND REEL**

Package Type	Reel Diameter	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	P1 (mm)	P2 (mm)	W (mm)	Pin1 Quadrant
WLCSP-2.0×2.4-30B	7"	9.0	2.15	2.55	0.75	4.0	4.0	2.0	8.0	Q1

#### **CARTON BOX DIMENSIONS**



NOTE: The picture is only for reference. Please make the object as the standard.

#### **KEY PARAMETER LIST OF CARTON BOX**

Reel Type	Length (mm)			Pizza/Carton	
7" (Option)	368	227	224	8	
7"	442	410	224	18	